

GSM-20H10 Source Meter

Cooper Liu

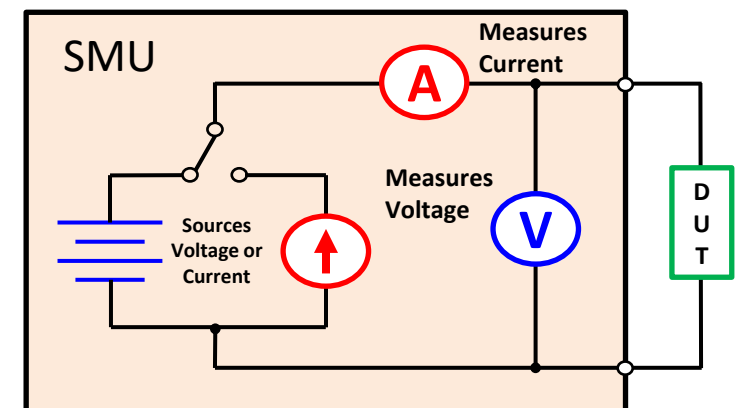
Outline

- Introduce Source Meters (SMU)
- Main Features
- Applications of SMU

Introduce Source Meters (SMU)

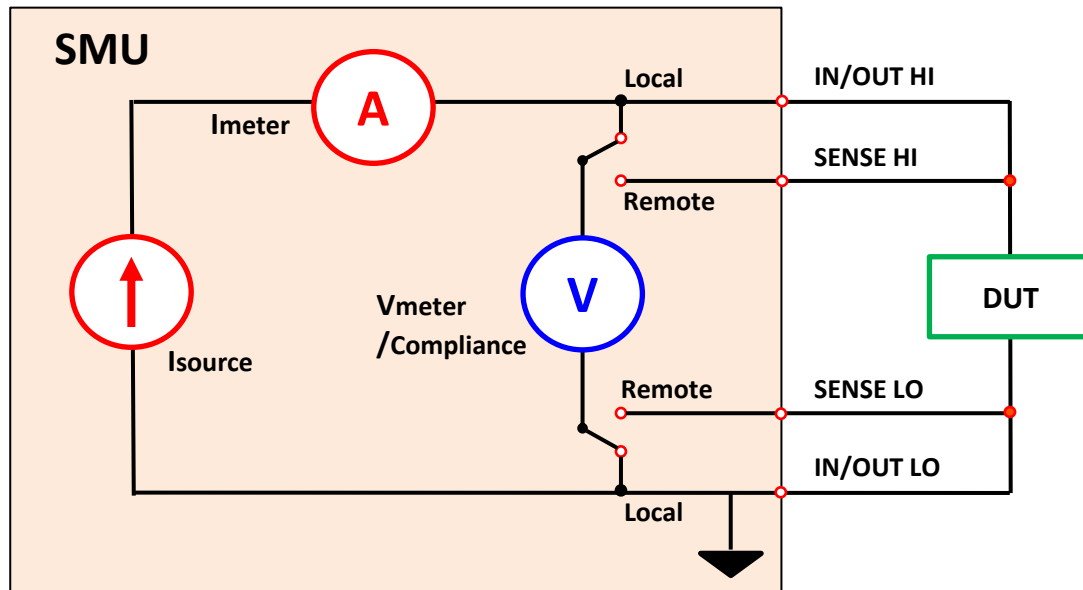
What is Source Meter?

- Main functions and features
 - Four-quadrant power supply and DMM function
 - Low power supply wattage, high voltage/current resolution
 - Measuring voltage/low current/resistance (high resolution)
 - High measuring speed requirement

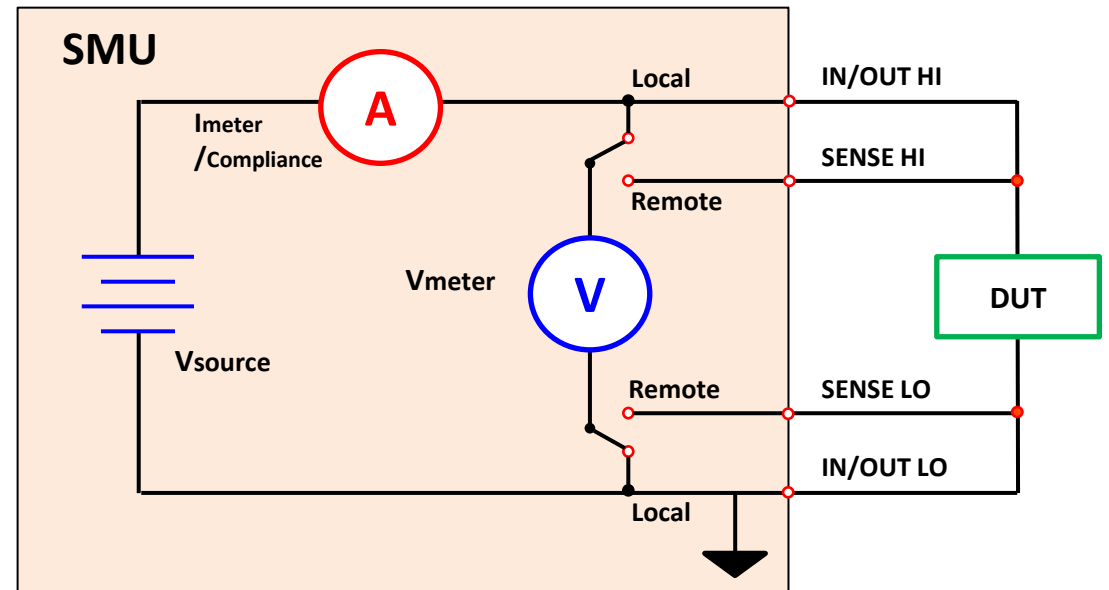


What is Source Meter?

- Main functions and features



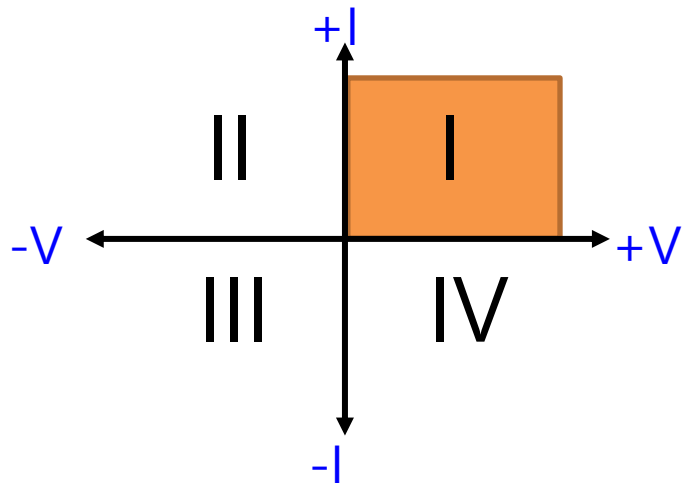
Source I, Measure V, I, Ω



Source V, Measure I, V, Ω

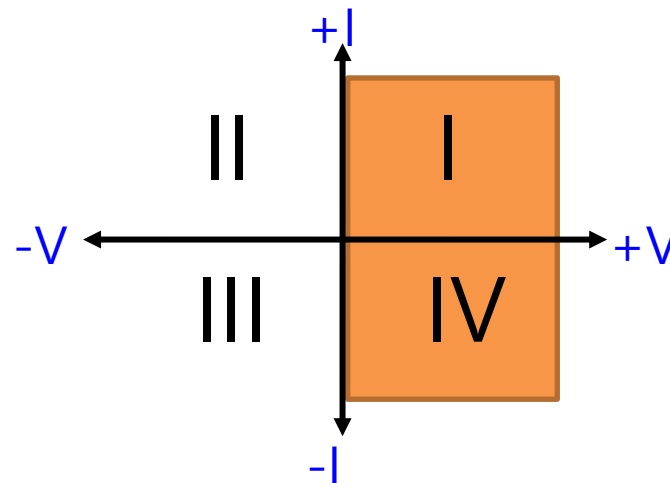
What is Source Meter?

- Type of power supply



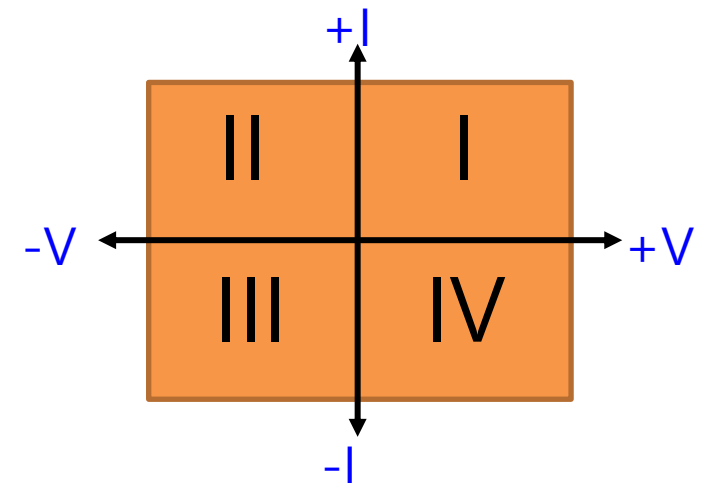
General power supply
GPP/GPE/PSW...

(Terminal outputs V/I,
current is irreversible.)



Power supply with sink function
PPH...

(Current can be injected.)



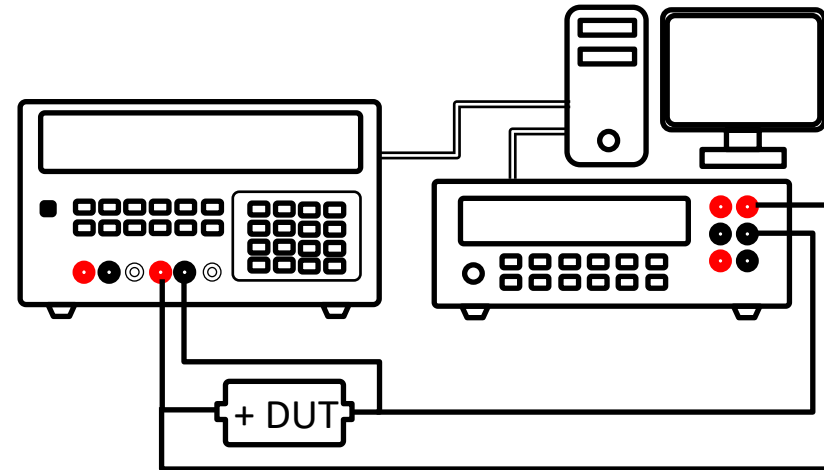
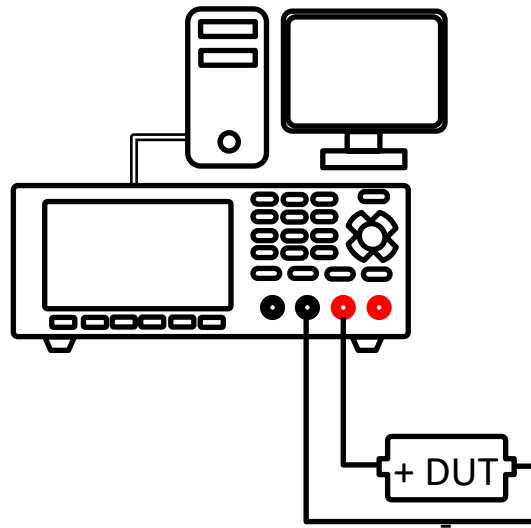
Source Meter
GMS-20H10

Bipolar DC Power Supply

(V/I input and output can be performed.)

What is Source Meter?

- **Advantages over Power Supply + DMM**
 - Saves space
 - Simplifies the wiring connection

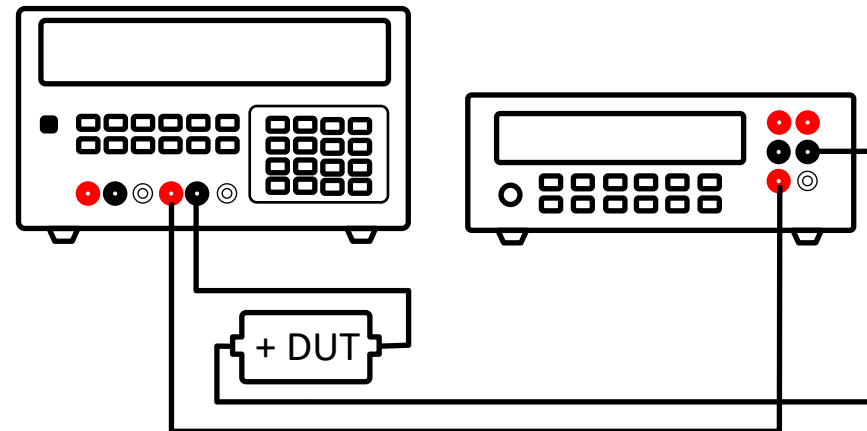
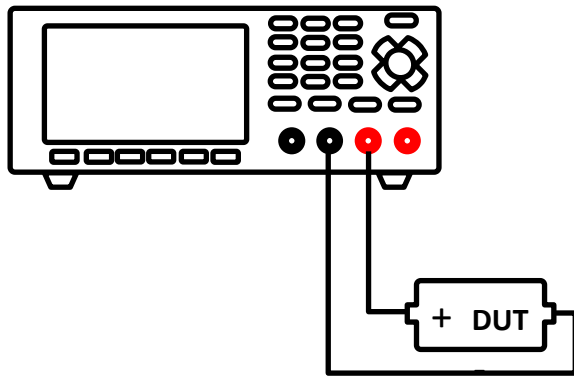


Measure voltage by power supply and DMM

What is Source Meter?

- **Advantages over Power Supply + DMM**

- Saves space
- Simplifies the wiring connection
- No need to re-wire in between voltage meter and current meter



Measure voltage by power supply and DMM

What is Source Meter?

- Name:
 - **System SourceMeter® (Tek/Keithley Trademark Reg.)**
 - **Precision Source / Measure Units (Keysight used often)**
 - **Source Meter**
 - **DC Voltage/Current Source/Monitor**
 - **SMU**

Main Features

Main Features

Source:

- Maximum output $\pm 210\text{V}$, $\pm 1.05\text{A}$, 22W
- Built-in 4 sequence output modes, up to 2500 points
- OVP /OTP Protection Function

Meter:

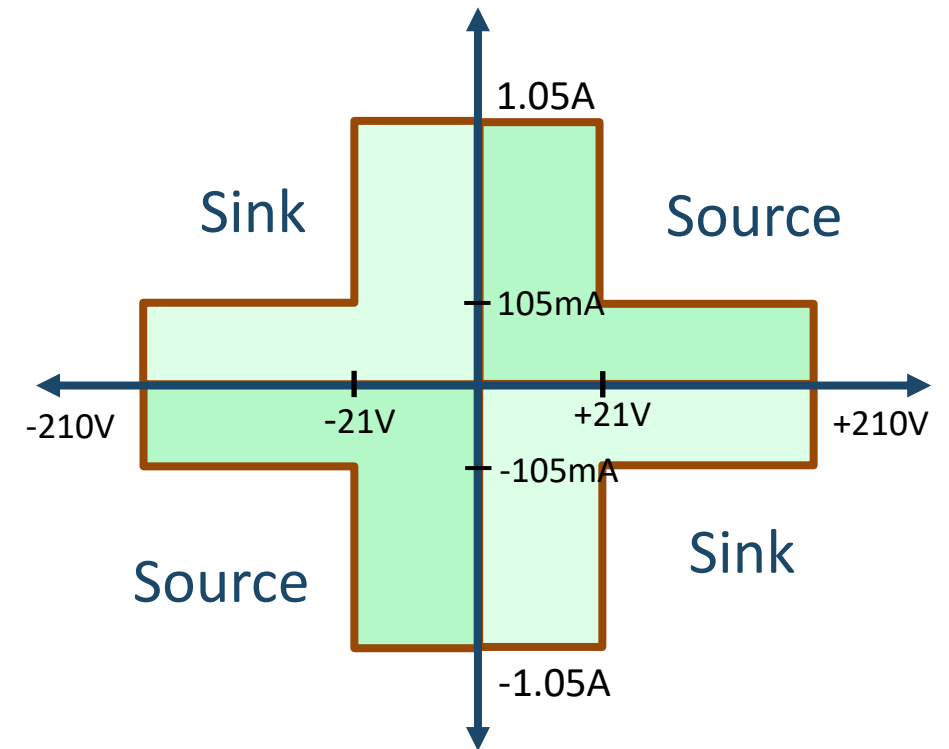
- 0.012% basic measure accuracy with 6½-digit resolution
- Variable Sampling Speed
- SDM (Source Delay Measure) cycle
- 2-, 4-, and 6-wire remote V-source and measure sensing
- Variable Display Digits
- Built-in Limit function
- Built-in 5 calculation functions

Others:

- Standard SCPI command, Provide Interface: RS-232, USBTMC, LAN, GPIB (Optional)
- 4.3" TFT LCD, Digital Number Keypad
- Built-in RTC Clock

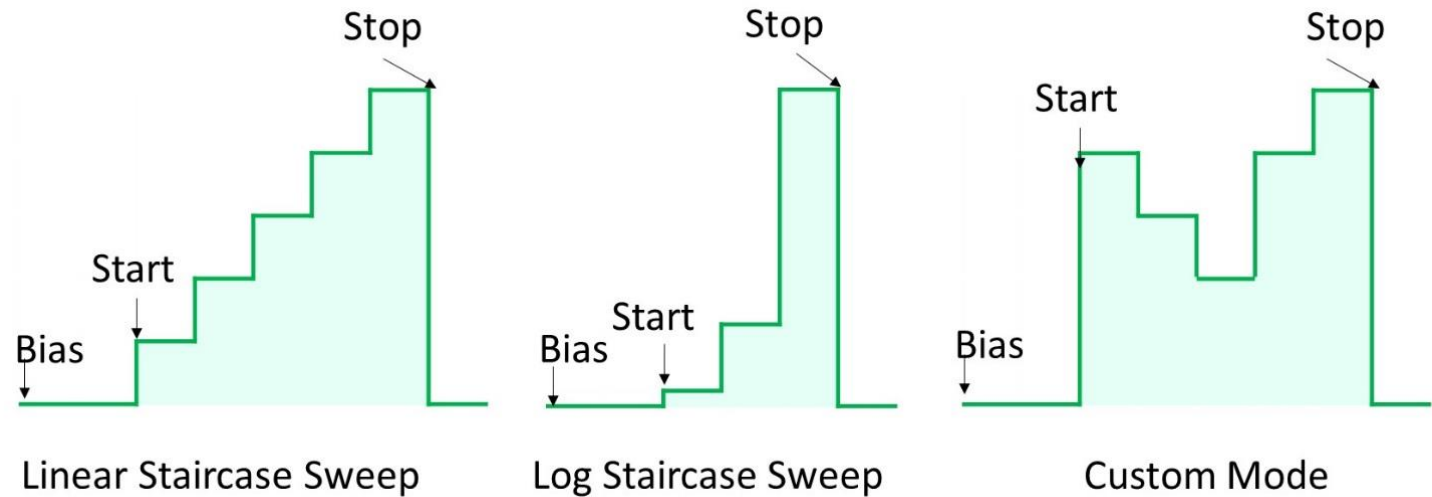
Main Features - Source

- Maximum output: $\pm 210\text{V}/\pm 1.05\text{A}/22\text{W}$
 - $\pm 21\text{V}$ up to 1.05A
 - $\pm 210\text{V}$ up to 105mA
 - Max Power : 22W



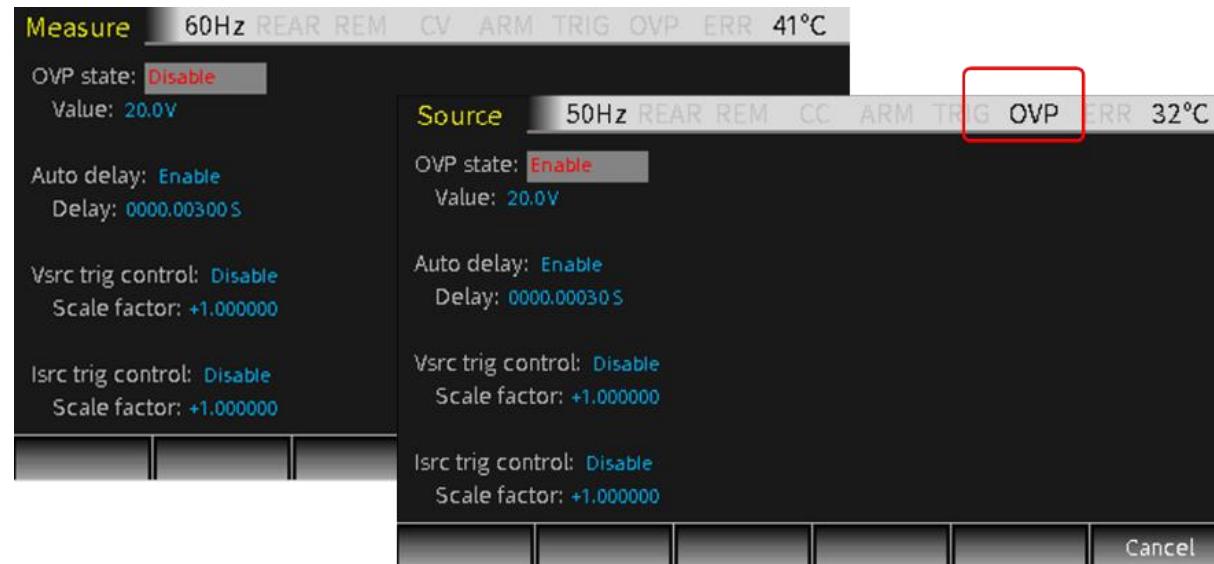
Main Features - Source

- Built-in 4 sequence output modes, up to 2500 points
 - Linear Stair
 - Log Stair
 - SRC-MEM
 - Custom



Main Features - Source

- OVP /OTP Protection Function

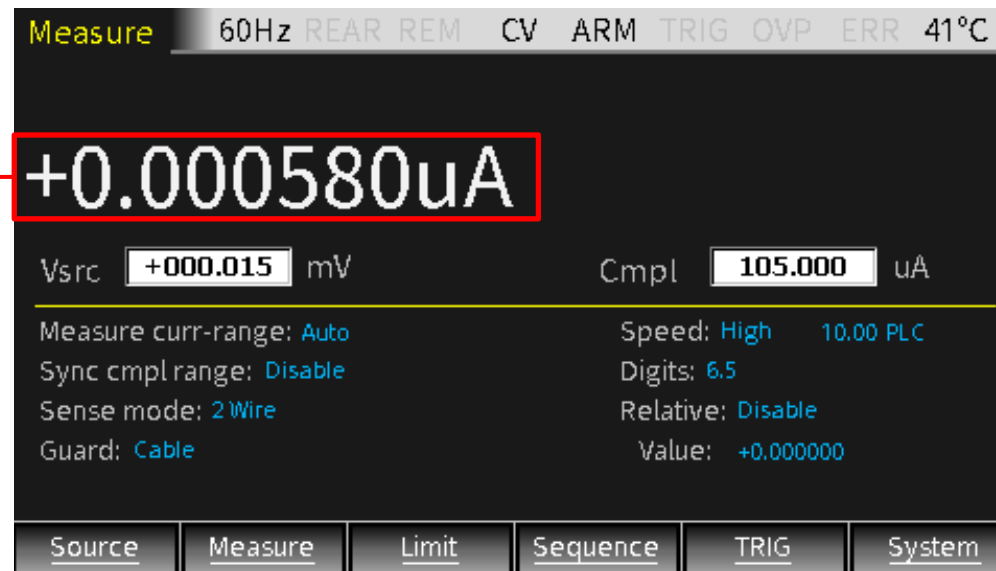


Main Features - Meter

- 0.012% basic measure accuracy with 6½-digit resolution

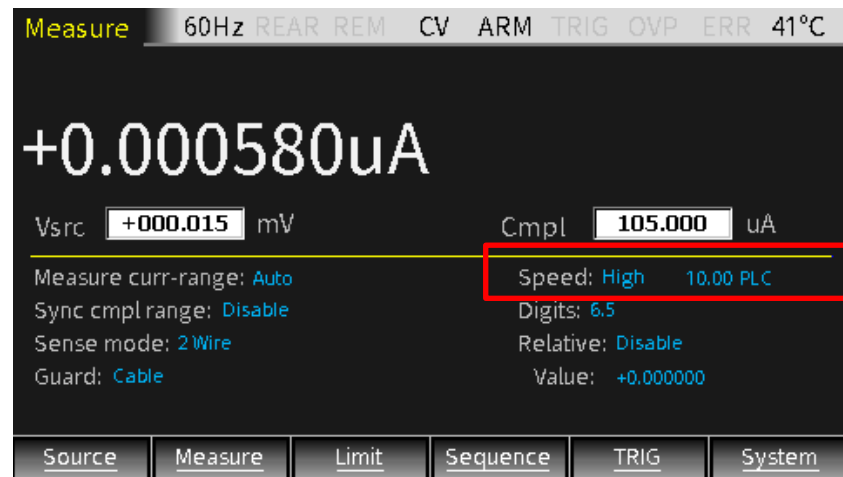
Voltage Range	±200.000mV	±2.00000V	±20.0000V	±200.000V
Measurement Resolution	1uV	10uV	100uV	1mV
Measurement Accuracy	±(0.012%+300uV)	±(0.012%+300uV)	±(0.015%+1.5mV)	±(0.015%+10mV)

6½-digit



Main Features - Meter

- Variable Sampling speed (High/Normal/Medium/Fast/Other)

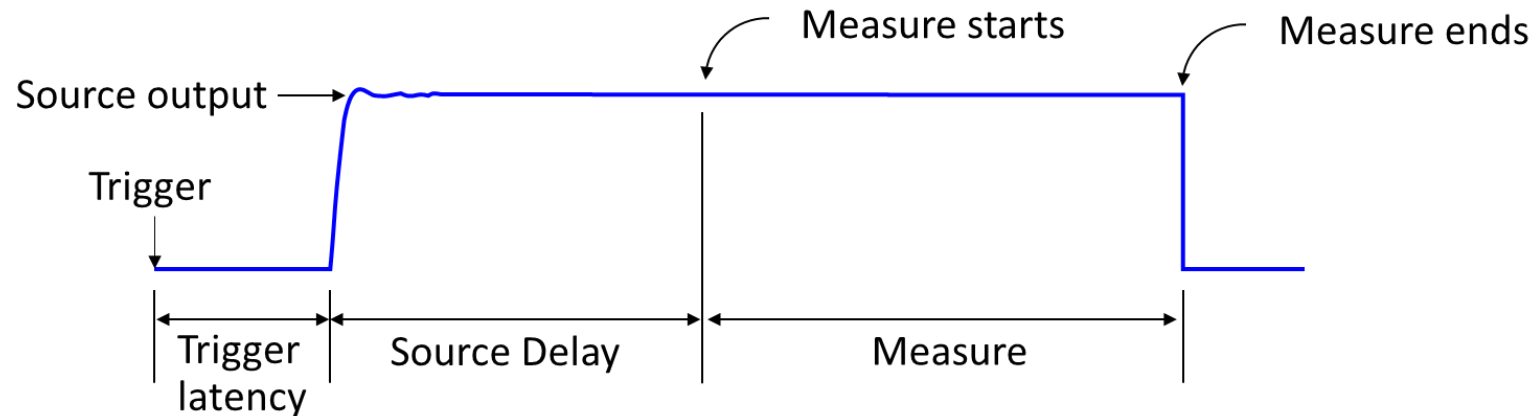


Variable Sampling speed

Sampling mode	Fast	Medium	Normal	High	Other
Speed, NPLC	0.01	0.1	1	10	User defined
Digit	3½	4½	5½	6½	Selectable

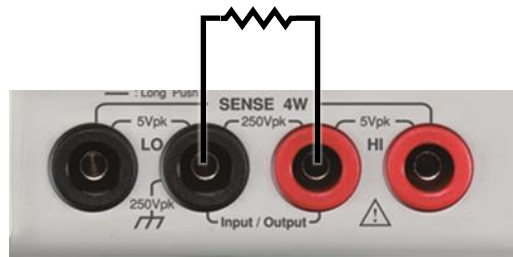
Main Features - Meter

- SDM (Source Delay Measure) cycle
 - When the signal changes, the sampling delay can be programmed or edited or adjusted, which is useful for the circuit under test to stabilize before the measurement.

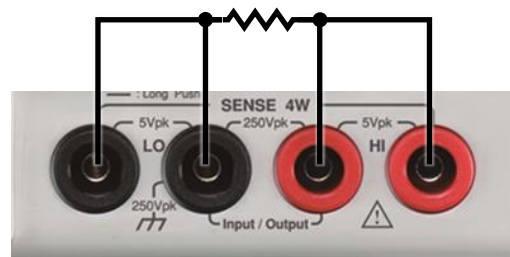


Main Features - Meter

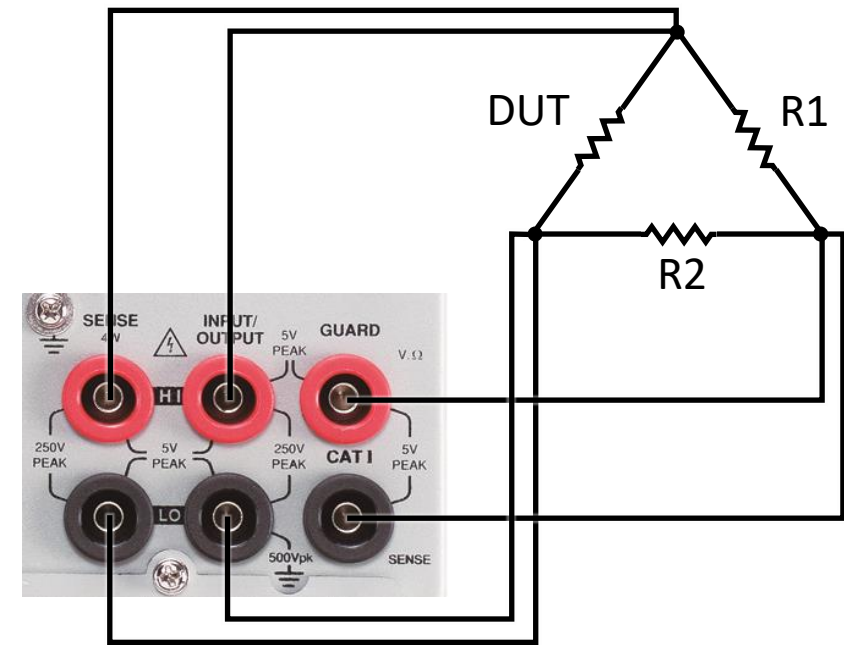
- 2, 4, and 6-wire remote V-source and measure sensing



2-wire



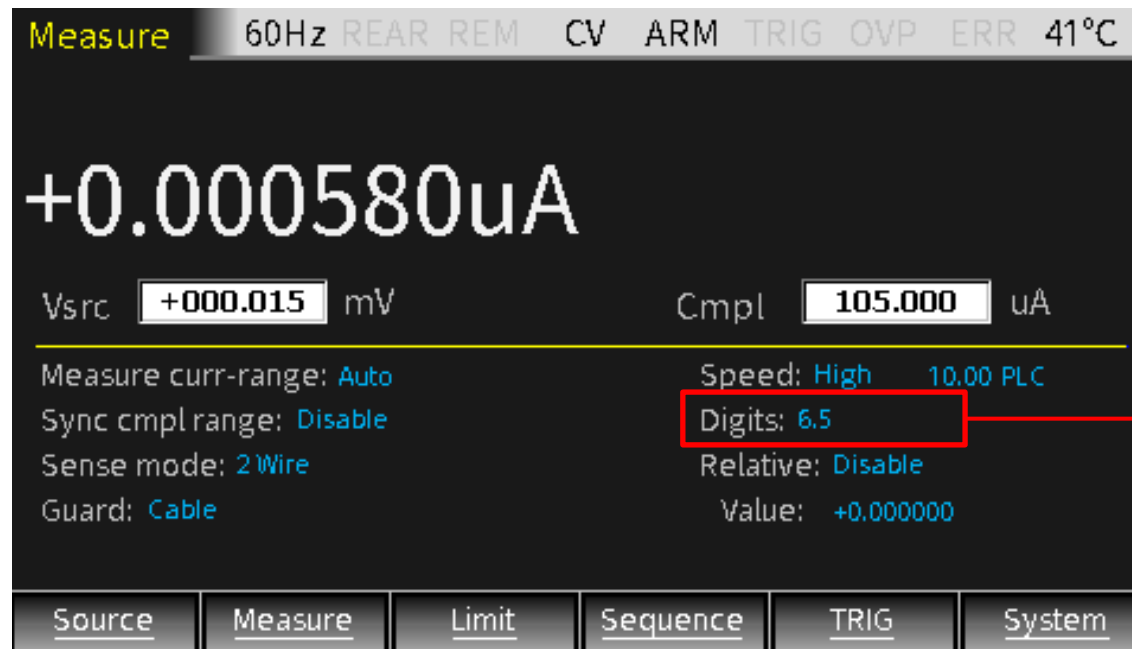
4-wire



6-wire

Main Features - Meter

- Display digits (3.5/4.5/5.5/6.5) variable



Adjustable display digits

Main Features - Meter

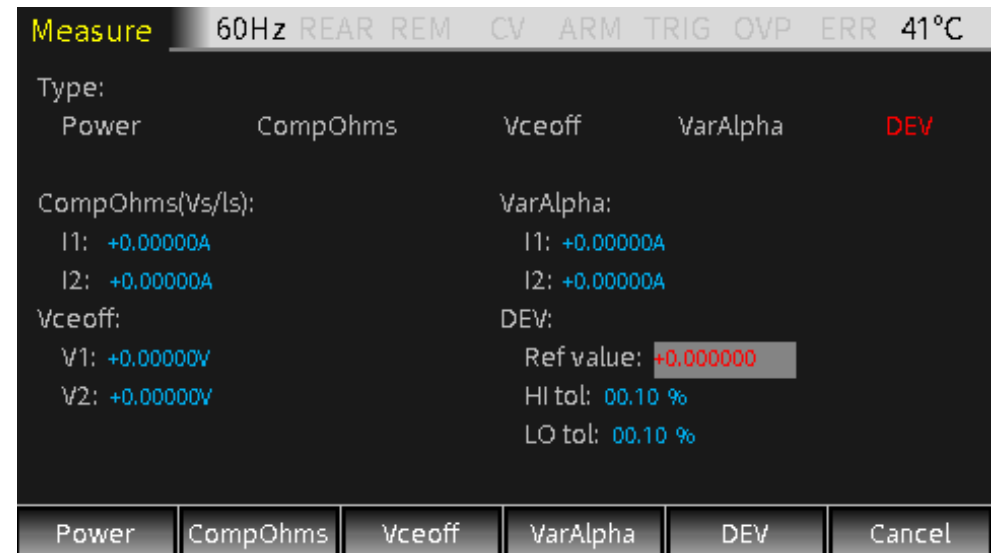
- Built-in Limit function, supports 11 groups of Limit tests (PASS/FAIL)

Limit	60Hz	REAR	REM	CV	ARM	TRIG	OVP	ERR	41°C
Digout size: 16bit									
Mode: Grading									
Sorting fail: 0									
Grading: Immediate									
Auto clear: Disable									
Clear pattern: 15									
Clear delay: 0.00010									
HW-Control: Disable									
Fail mode: In									
CMPL pattern: 15									
Pass pattern: 7									
Source memory location: Next									
Location: 1									
End of test mode: EOT									
Digout	HW-Limits	SW-Limits	Pass	EOT-Mode	Cancel				

Limit	60Hz	REAR	REM	CV	ARM	TRIG	OVP	ERR	41°C
	Low			Lo_fail			High		Hi_fail
L02: Disable	-1.000000_			15			+1.000000_		15
L03: Disable	-1.000000_			15			+1.000000_		15
L05: Disable	-1.000000_			15			+1.000000_		15
L06: Disable	-1.000000_			15			+1.000000_		15
L07: Disable	-1.000000_			15			+1.000000_		15
L08: Disable	-1.000000_			15			+1.000000_		15
L09: Disable	-1.000000_			15			+1.000000_		15
L10: Disable	-1.000000_			15			+1.000000_		15
L11: Disable	-1.000000_			15			+1.000000_		15
L12: Disable	-1.000000_			15			+1.000000_		15
Digout	HW-Limits	SW-Limits	Pass	EOT-Mode	Cancel				

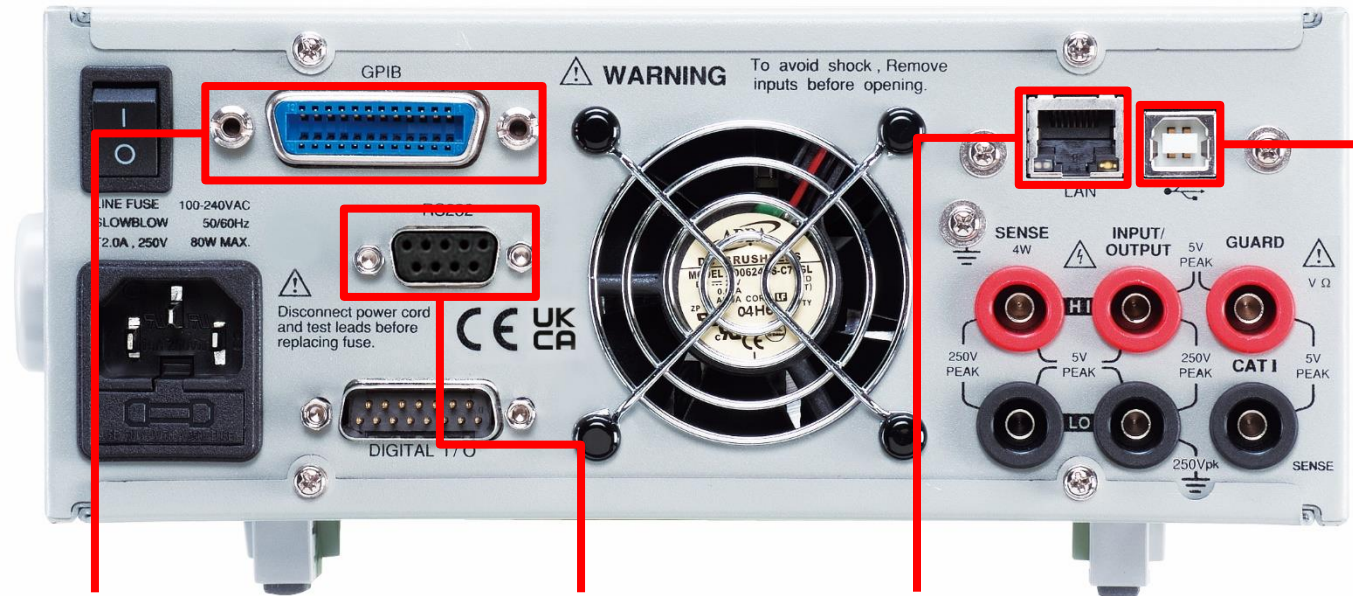
Main Features - Meter

- Built-in 5 calculation functions
 - Power, Power = V*I
 - Compensated Ohms, $\text{CompOhms} = \frac{(V2-V1)}{(I2-I1)}$
 - Voltage Coefficient, $\text{Vceoff}(\%) = \left[\frac{\Delta R}{\{R2*\Delta V\}} \right] * 100\%$
 - Varistor Alpha, $\text{VarAlpha } \alpha = \frac{\log(I2 \div I1)}{\log(v2 \div V1)}$
 - Percent Deviation, $\text{Dev} = \left[\frac{(X-Y)}{Y} \right] * 100\%$



Main Features - Other

- Standard SCPI RS-232 , USB-TMC, LAN, GPIB (Optional)



GPIB (Option)

RS-232

LAN

USB Device

Main Features - Other

- 4.3" TFT LCD, Digital Number Keypad
 - With the large 4.3-inch screen, all measurement settings, parameters and results can be completely displayed on the screen: the digital number keypad provides users with a more friendly input method.



4.3" TFT LCD Panel

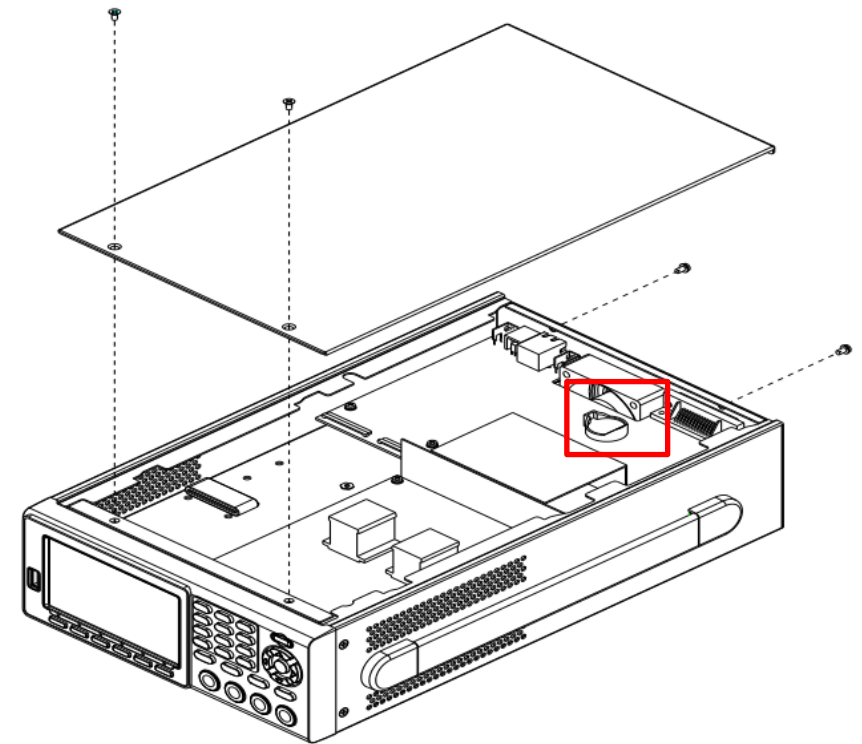
Digital input keypad



Keithley 2400 Dot-matrix display

Main Features - Other

- Built-in RTC clock
 - The built-in RTC Clock circuit allows users to record the time when storing the file, which is convenient for data comparison or recording.



Applications of SMU

Applications of SMU

No.	Test classification	DUT
1	Semiconductor Device Characterization Test	Resistors, Diodes, BJT Transistors, MOSFET Transistors, SiCs
2	Energy and Efficiency Characteristic Testing	LED, OLED Display, solar cell, battery, DC-DC converter
3	Sensor Characterization Test	Resistance characteristics, Hall effect
4	Organic Material Characterization Testing	E-ink, Printed electronics
5	Nanomaterial Characterization Testing	Graphene

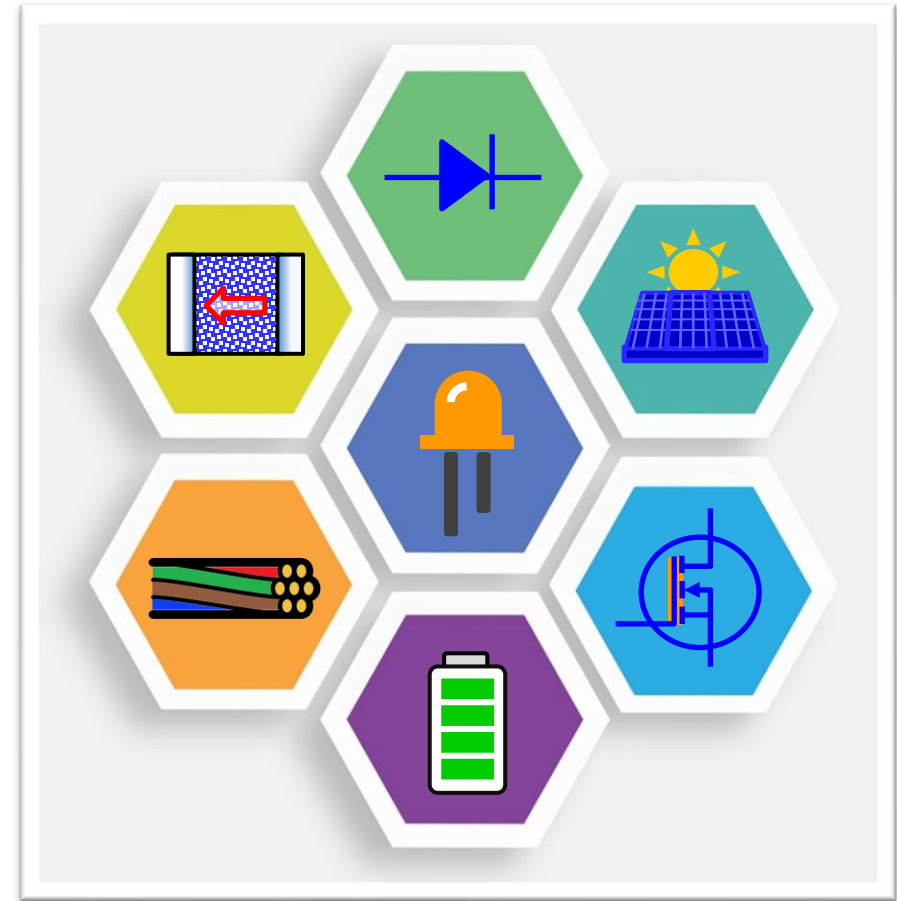
From: Tek/Keithley, Keysight, ADCMT..etc

Applications of SMU

Microcircuit		
1	IC	IV test, I/O curves
Component		
1	Diode	Forward conduction voltage, forward current, reverse breakdown voltage, reverse current
2	BJT	IV test, characteristic curve
3	MOSFET	IV test, characteristic curve
4	IGBT	IV test, characteristic curve
Battery		
1	Lithium battery	IV test, charge-discharge scan curve
2	Solar battery	IV test, discharge scan curve
Material		
1	Graphene	IV test, I/O curves
2	Carbon nanotube	IV test, I/O curves

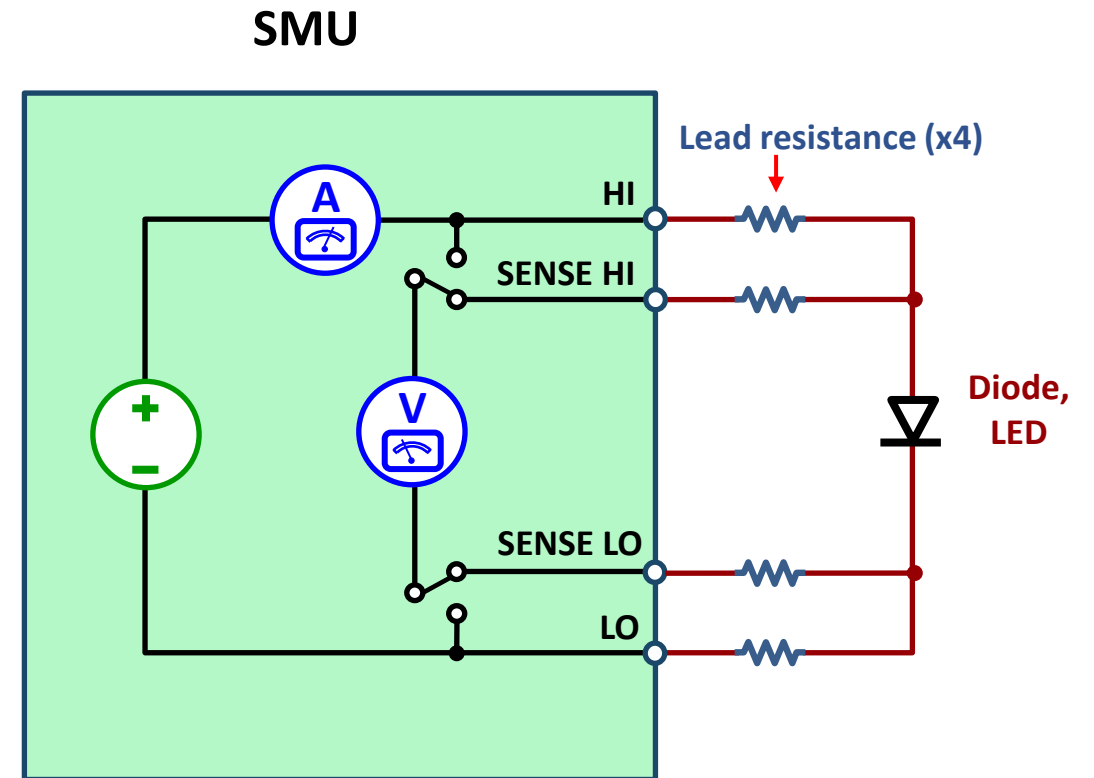
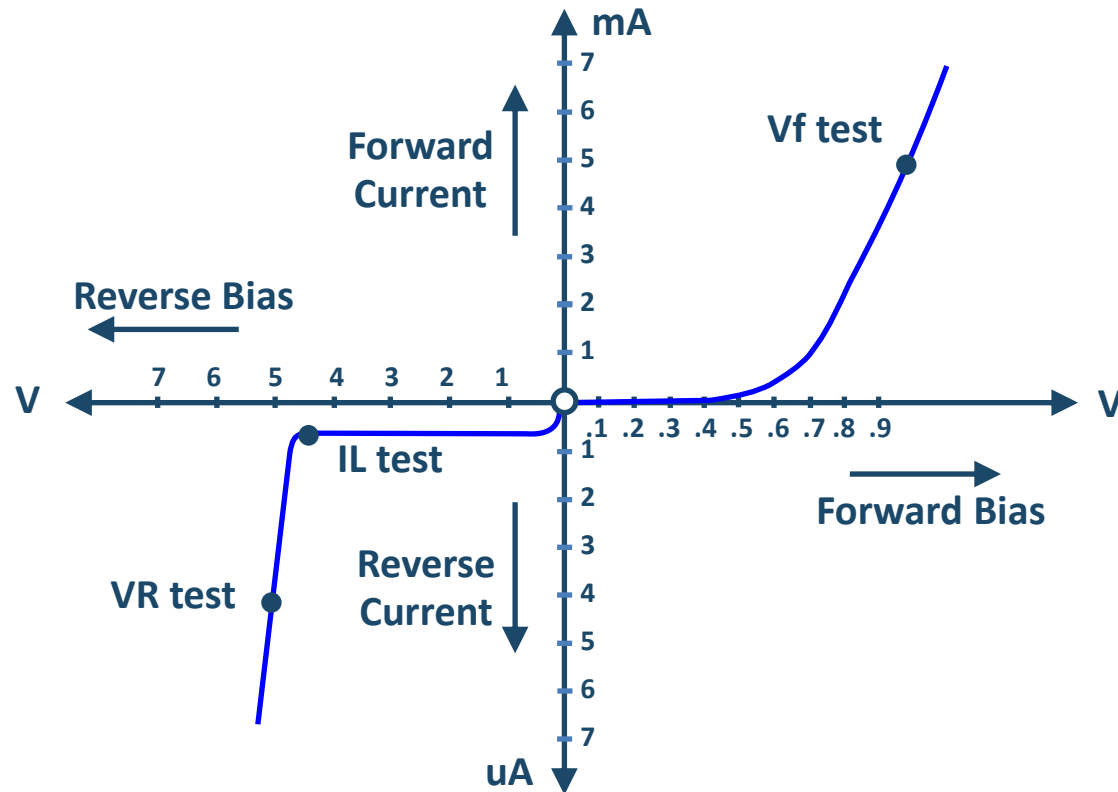
Applications of SMU

- Diode characteristics test
- Solar cell V-I characteristics test
- MOSFET characteristics test
- Battery charging and discharging test
- Precise low resistance measurement
- High resistance measurement
- LED thermal resistance measurement



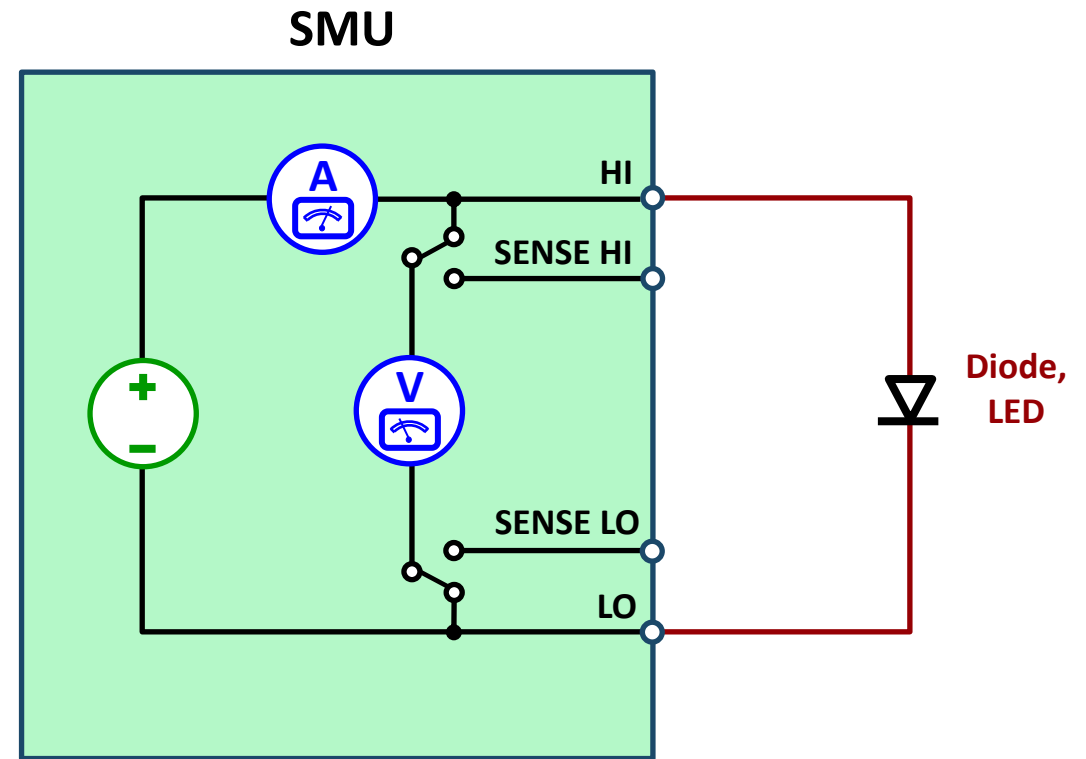
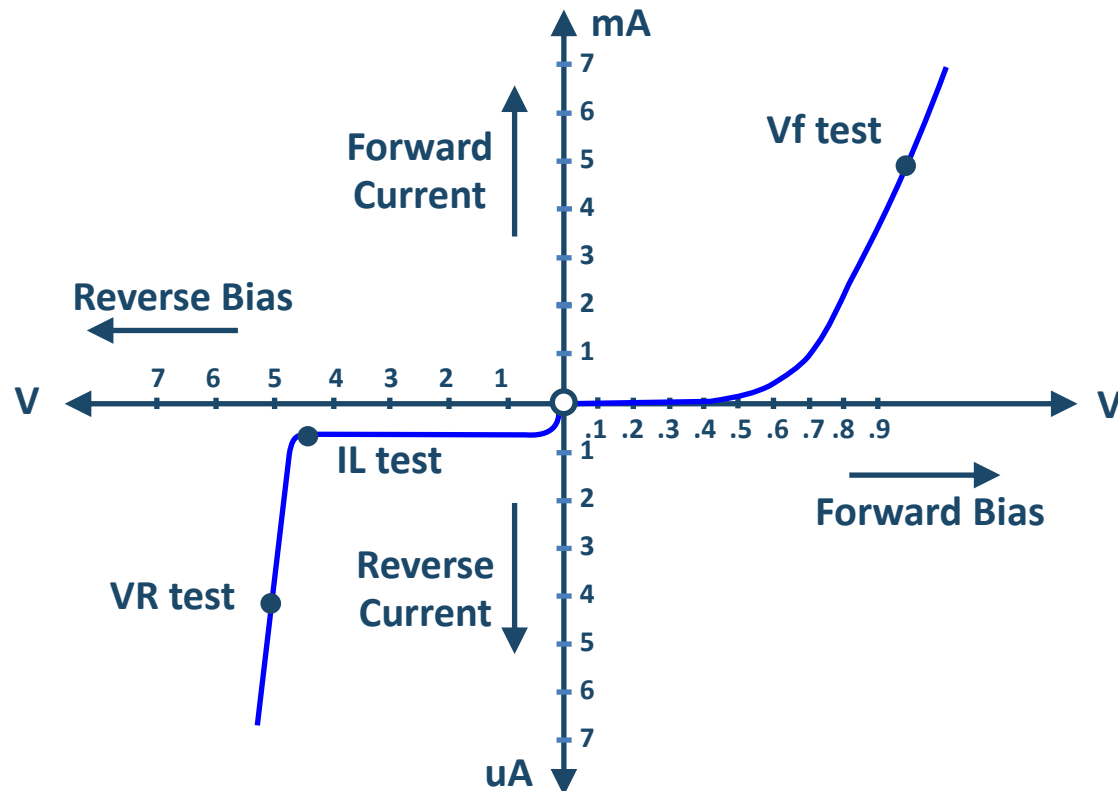
Diode, LED V-I characteristics test

- Forward bias test



Diode, LED V-I characteristics test

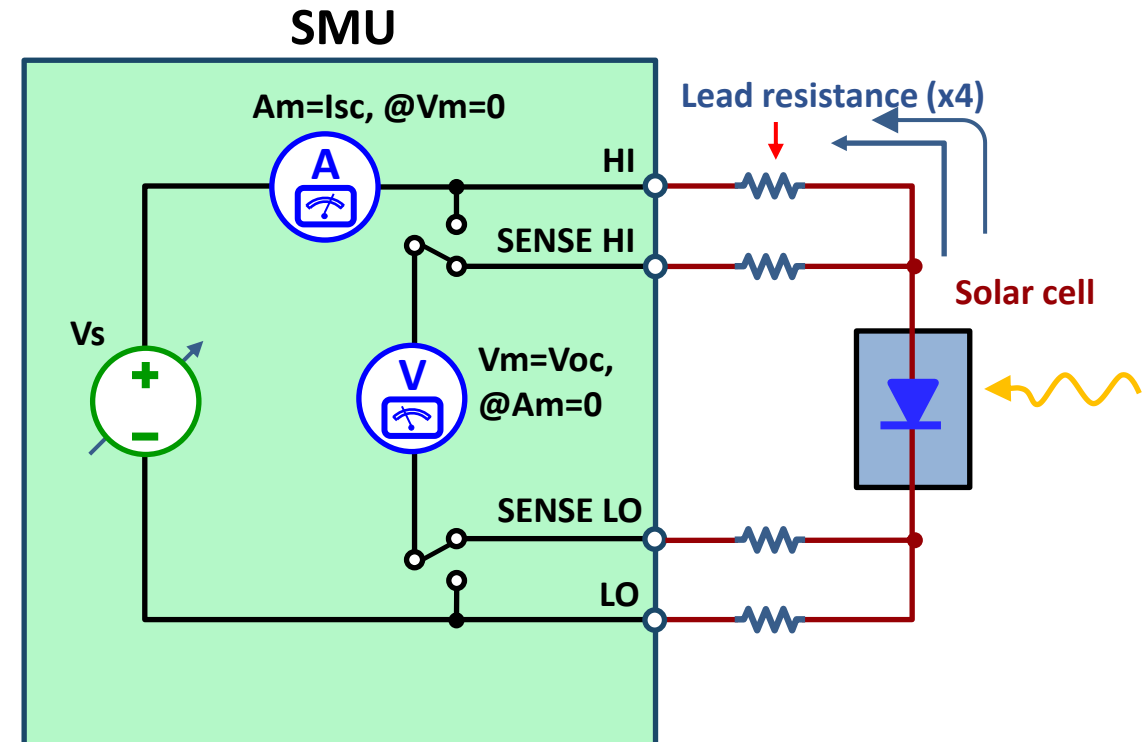
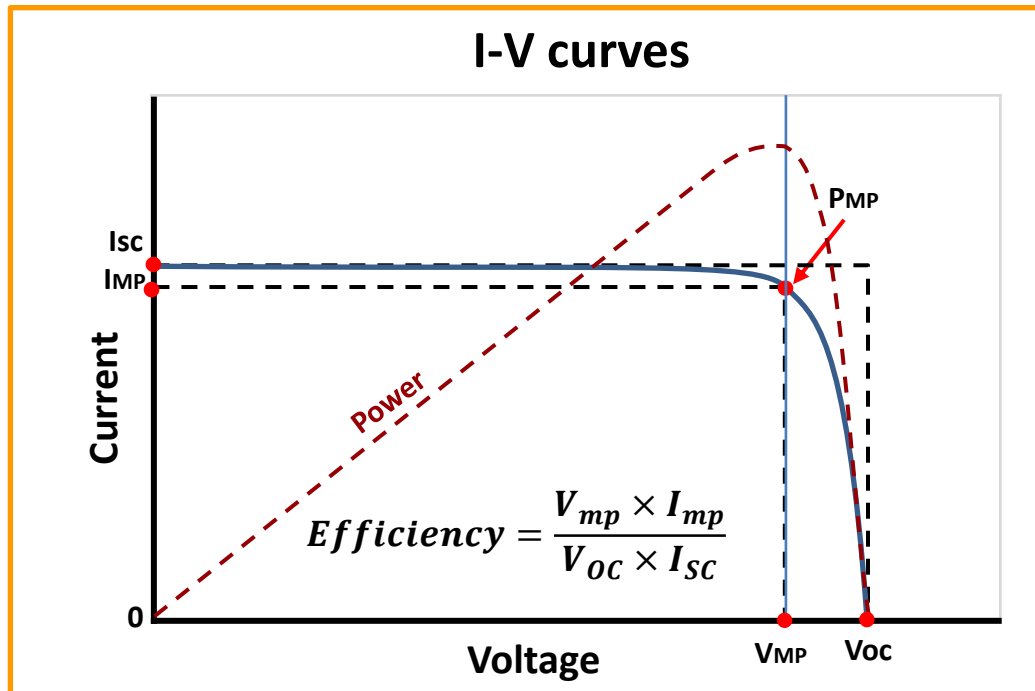
- Forward bias test
- Reverse bias test: leakage current, breakdown voltage



Solar cell V-I characteristics test

- Use SMU as load to obtain I_{sc} , V_{oc} , PMP (by $V_{MP} \times I_{MP}$) and get efficiency by

$$\text{Efficiency} = \frac{V_{mp} \times I_{mp}}{V_{oc} \times I_{sc}}$$



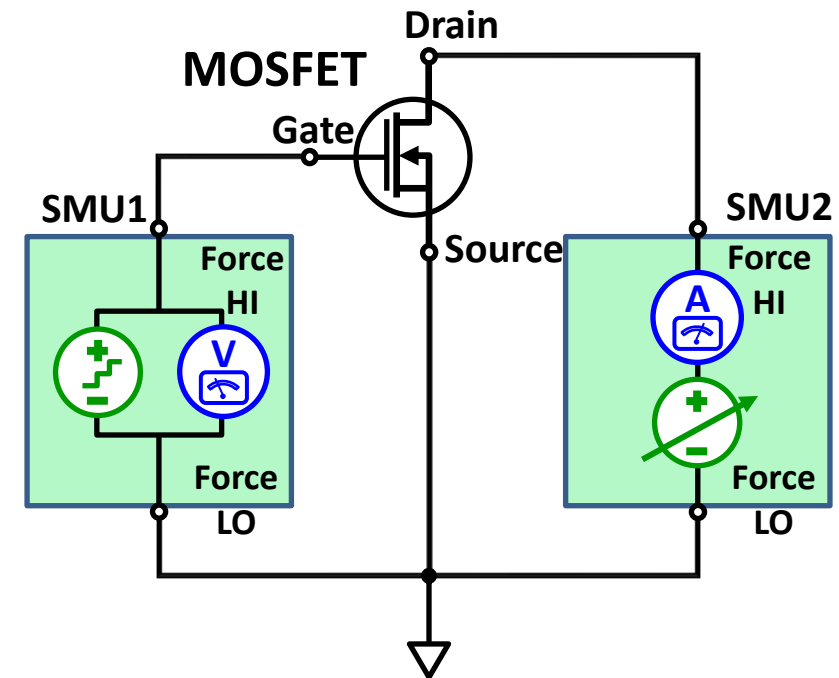
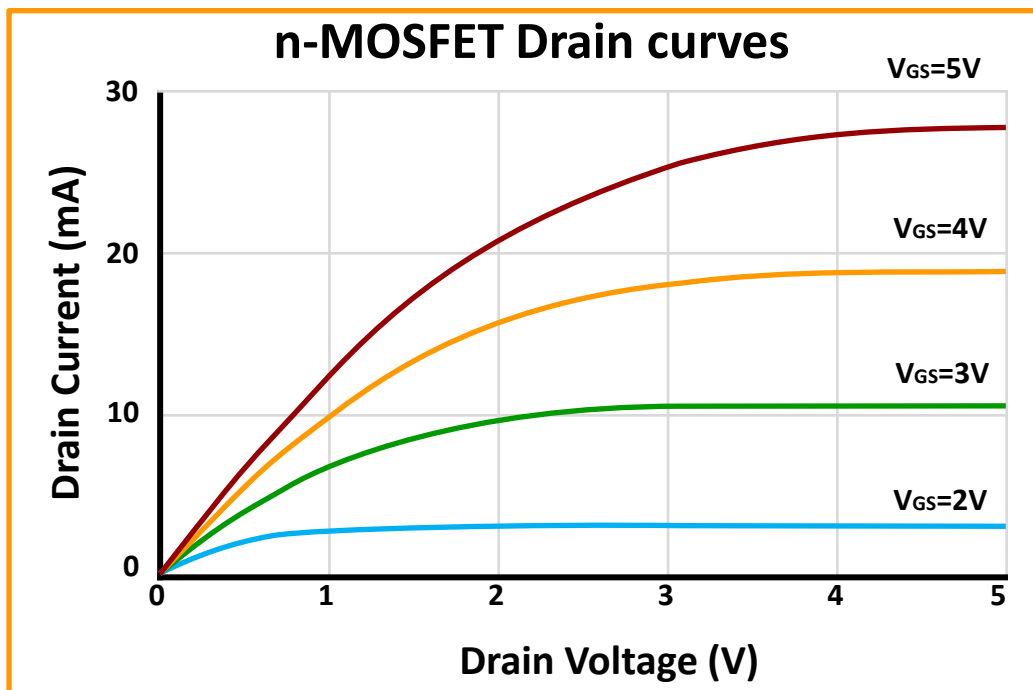
MOSFET characteristics test

- **Drain curves**
- **Threshold voltage**
- **Transconductance**
- **Gate leakage current**
- **Drain leakage Current**
- **Breakdown voltage**

MOSFET – Drain Curve

The most popular characteristic while use a MOSFET

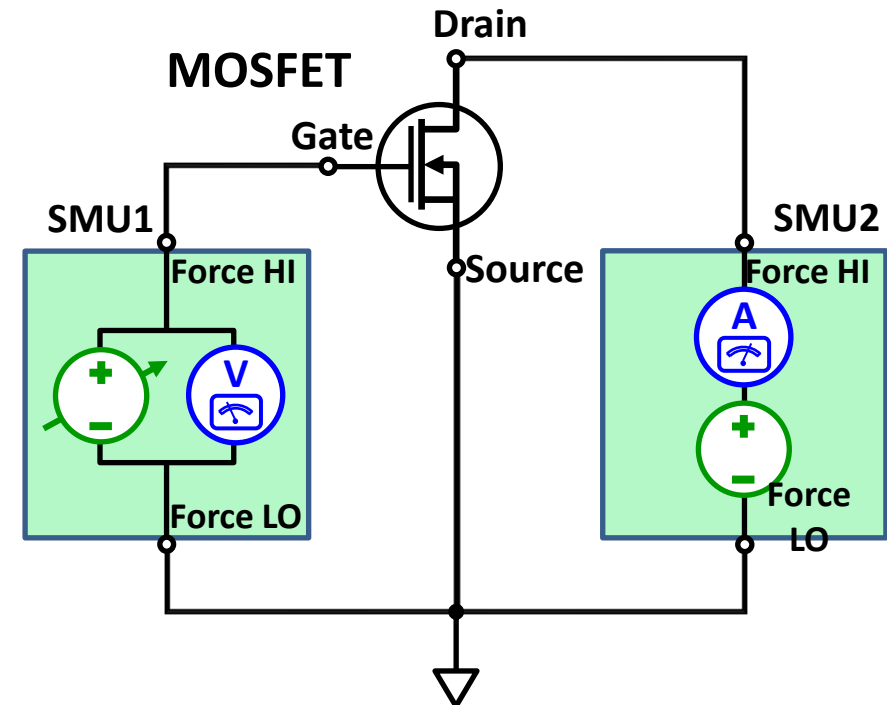
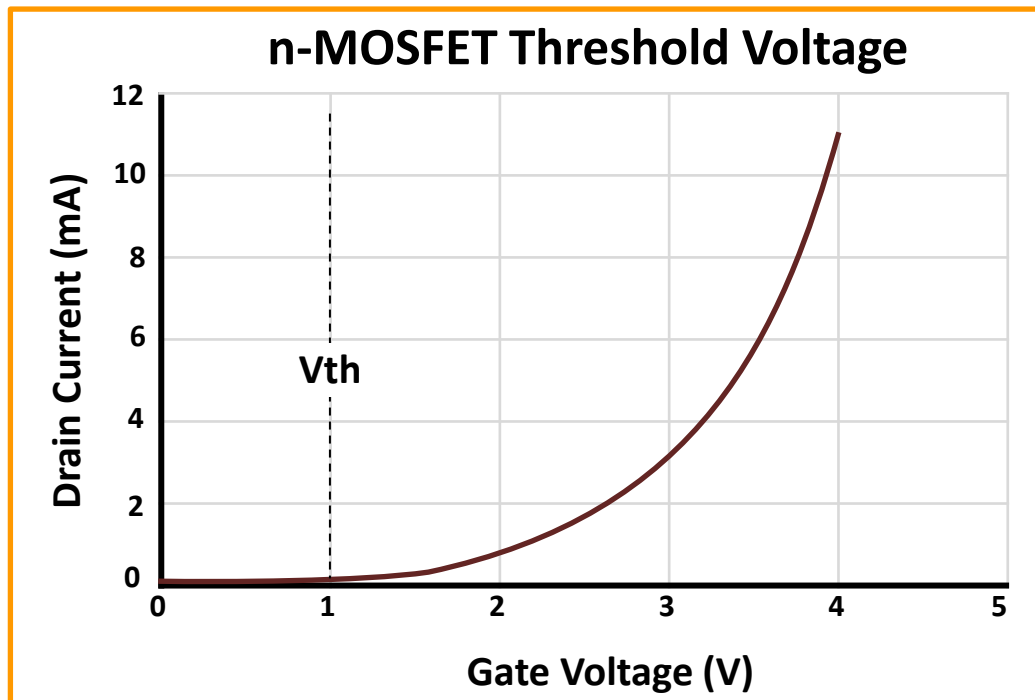
1. Use SMU1 to set V_{gs} , SMU2 to sweep V_{ds} , measure I_{ds} to get the curve
2. Set V_{gs} to other values, sweep V_{ds} to obtain the different curves.



MOSFET – Gate Threshold Voltage, V_{th}

V_{th} is the gate to source voltage that appears when the minimum I_{ds} flows from source to drain.

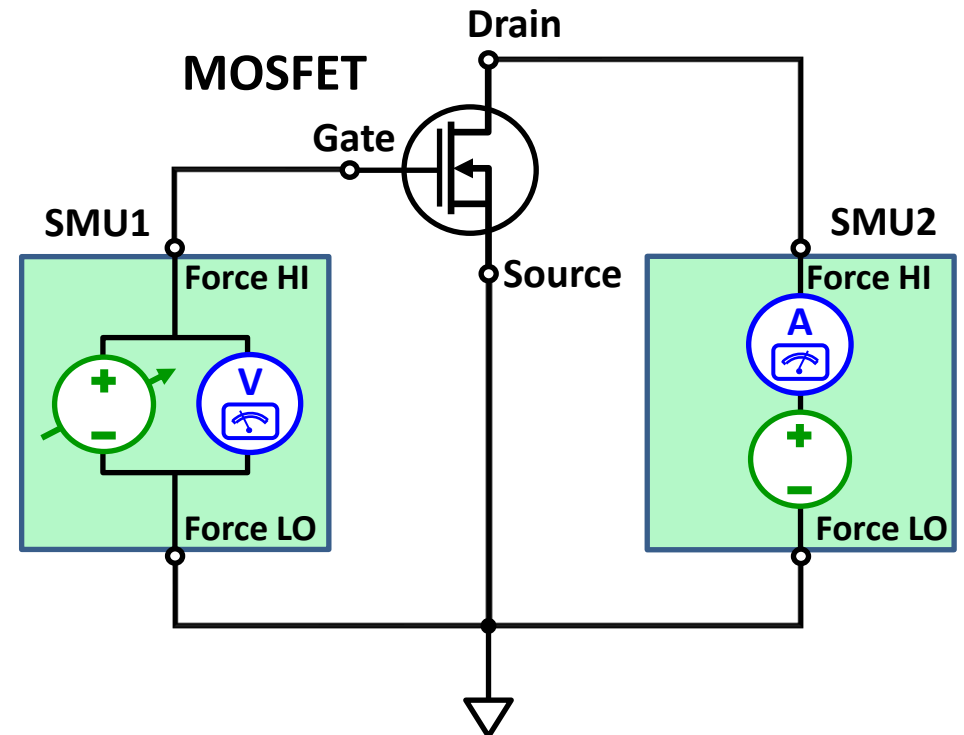
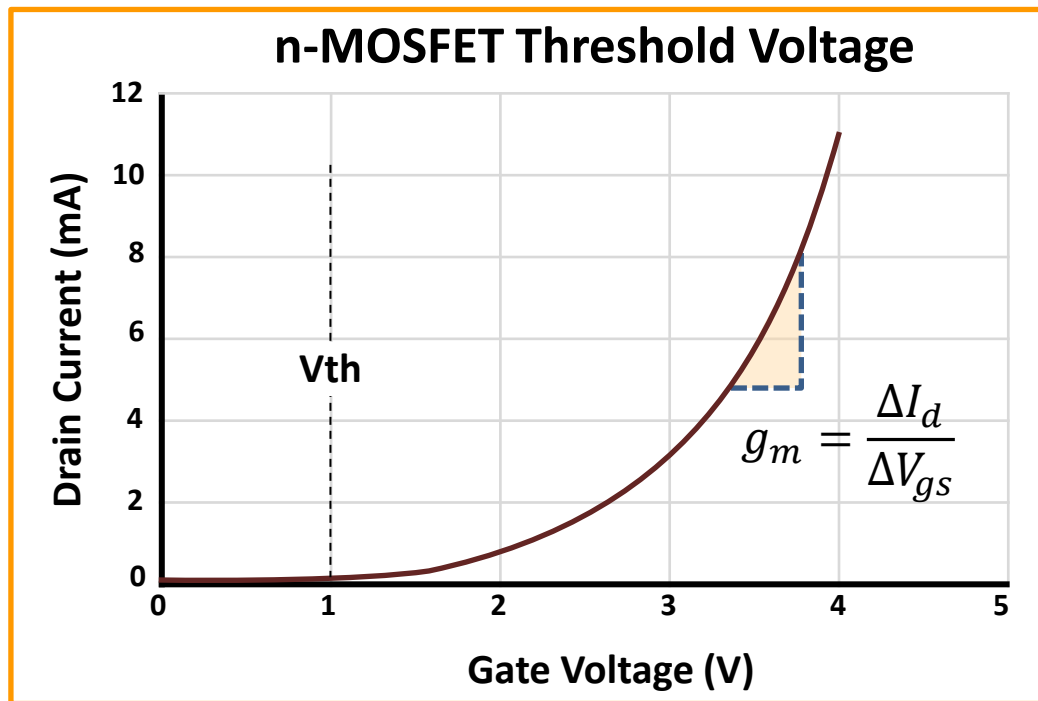
1. Set V_{ds} to a particular value with SMU2, which the minimum I_{DS} will occur.
2. Sweep V_{gs} with SMU1 until I_{DS} reaches the specified value. The V_{gs} is V_{th} .



MOSFET – Transconductance, gm

gm represents the signal gain of a MOSFET.

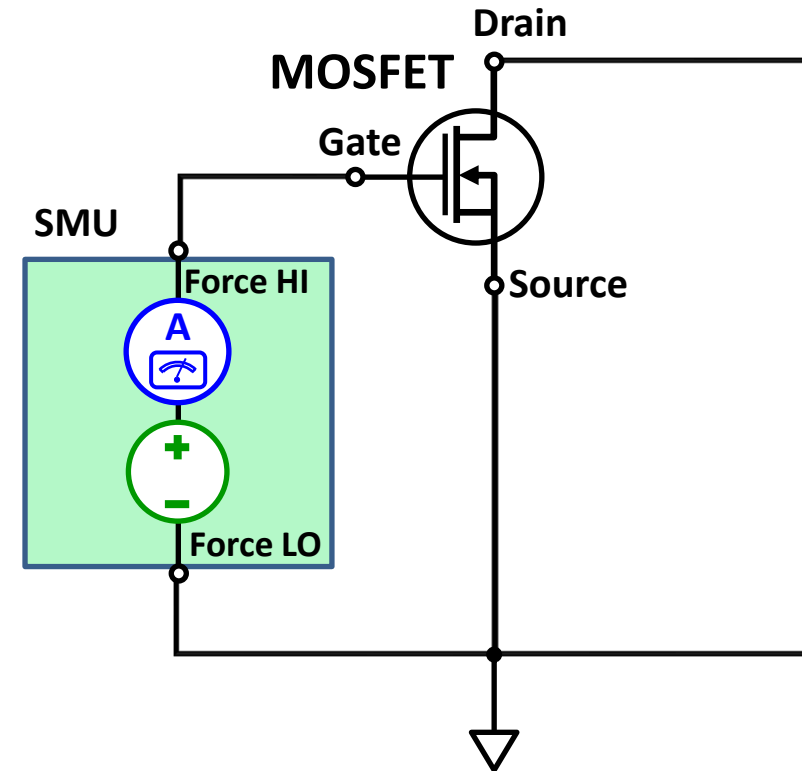
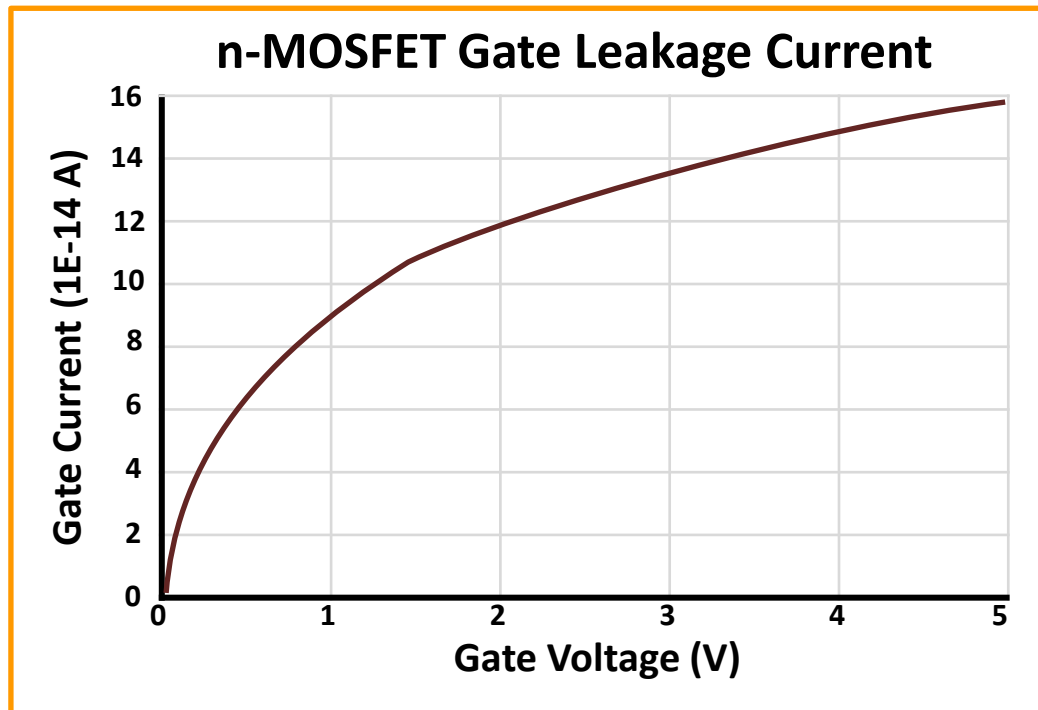
1. Set the constant voltage Vds with SMU2.
2. Sweep Vgs with SMU1 and measure Ids SMU2 current meter.



MOSFET – Gate leakage current, I_{gss}

I_{gss} is the current between the gate and source at $V_{DS} = 0$.

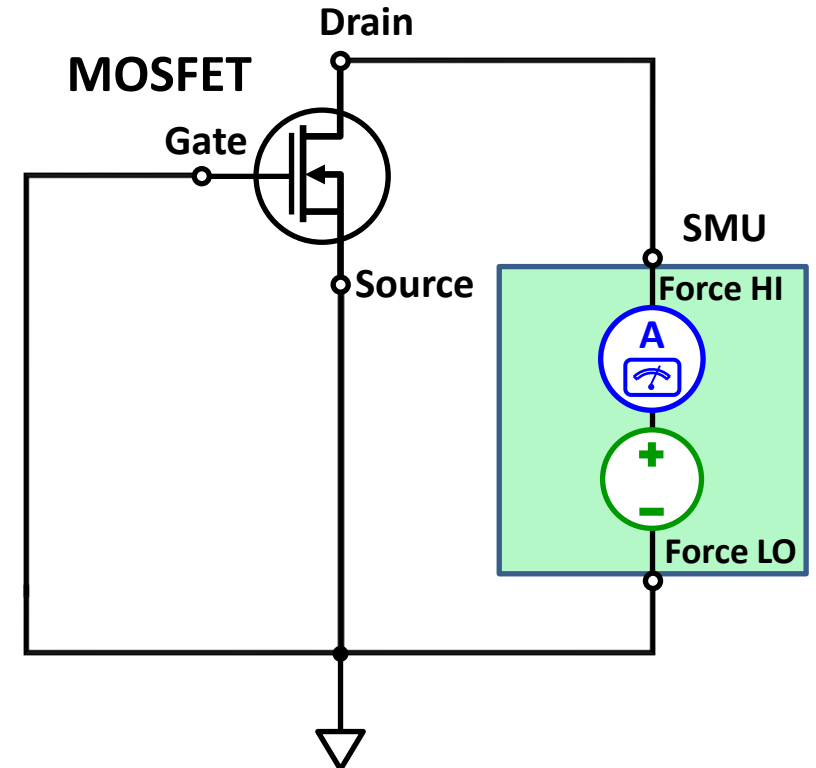
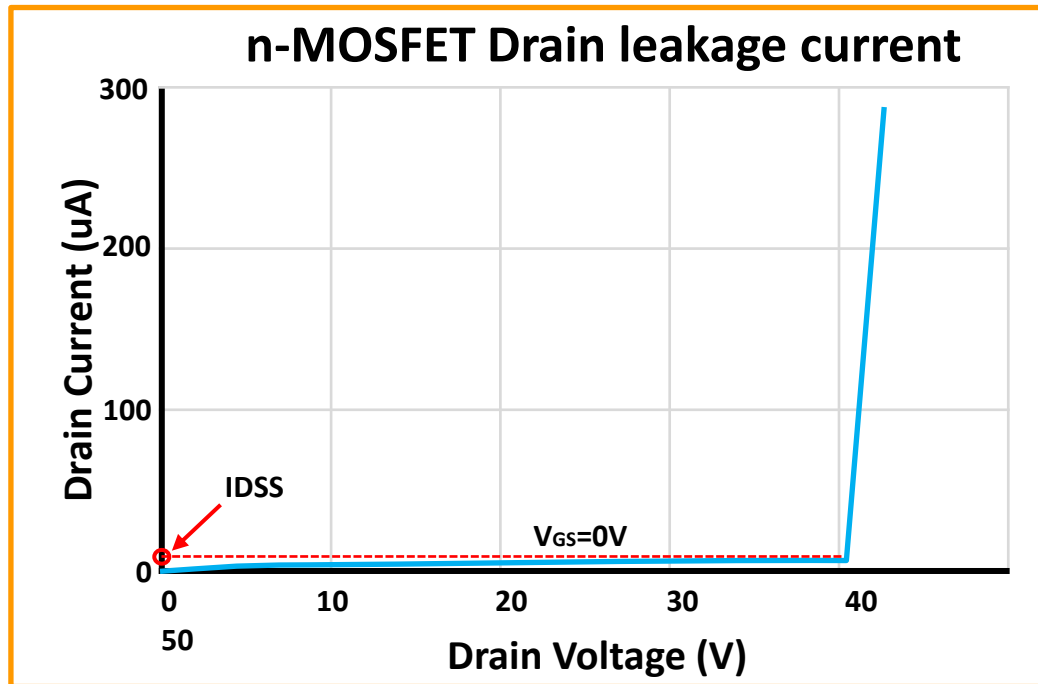
1. Short Drain and Source
2. Sweep V_{gs} over the desired range, measure the current.



MOSFET – Drain leakage current

I_{DSS} is the current between the drain and source at $V_{GS} = 0$.

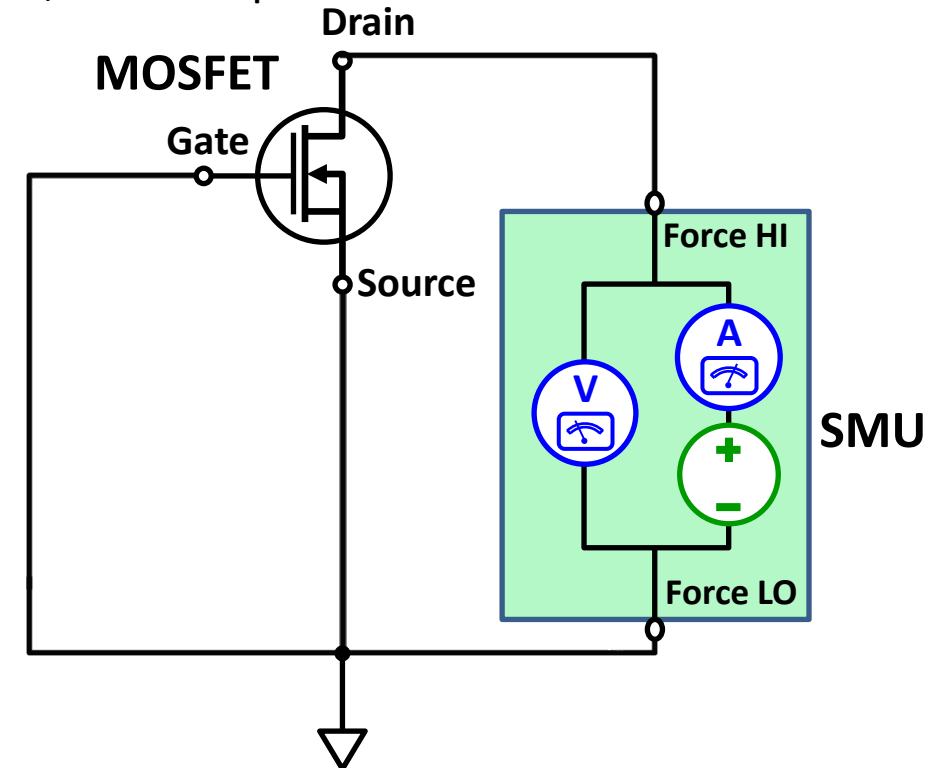
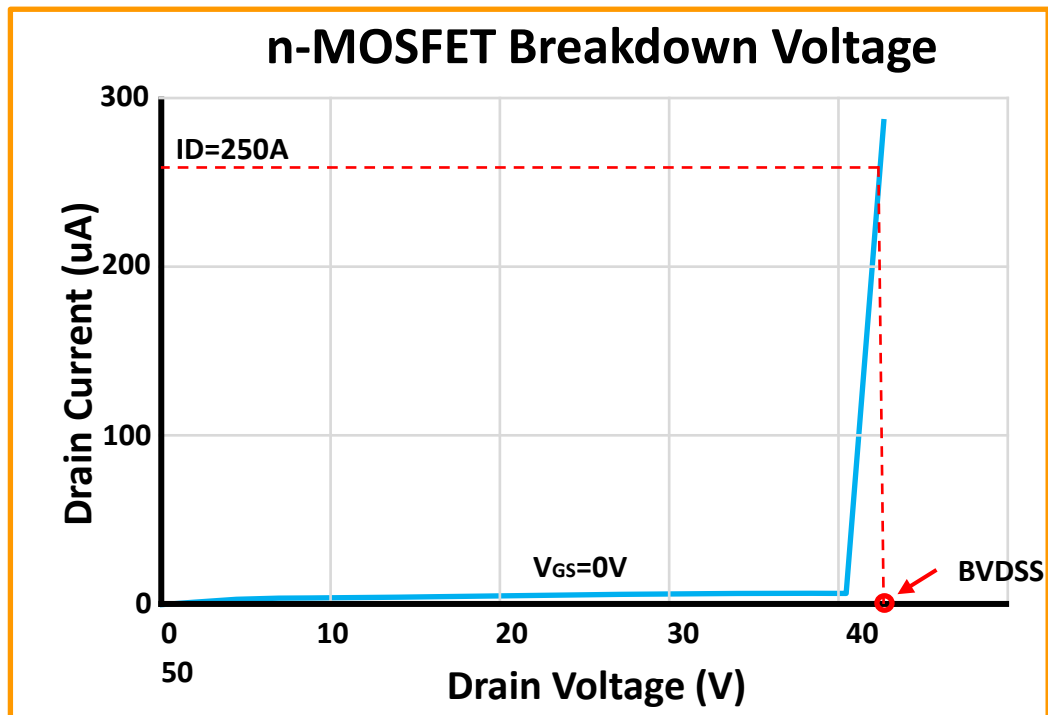
1. Short Gate and Source
2. Sweep V_{ds} and monitor the leakage current of Drain-Source



MOSFET – Drain Source Breakdown voltage, BVdss

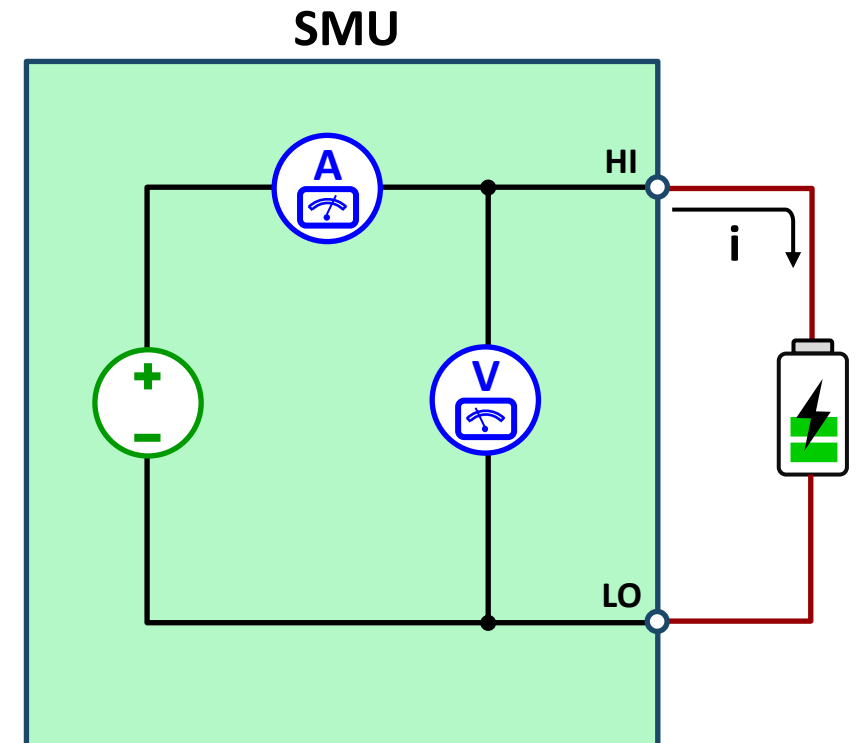
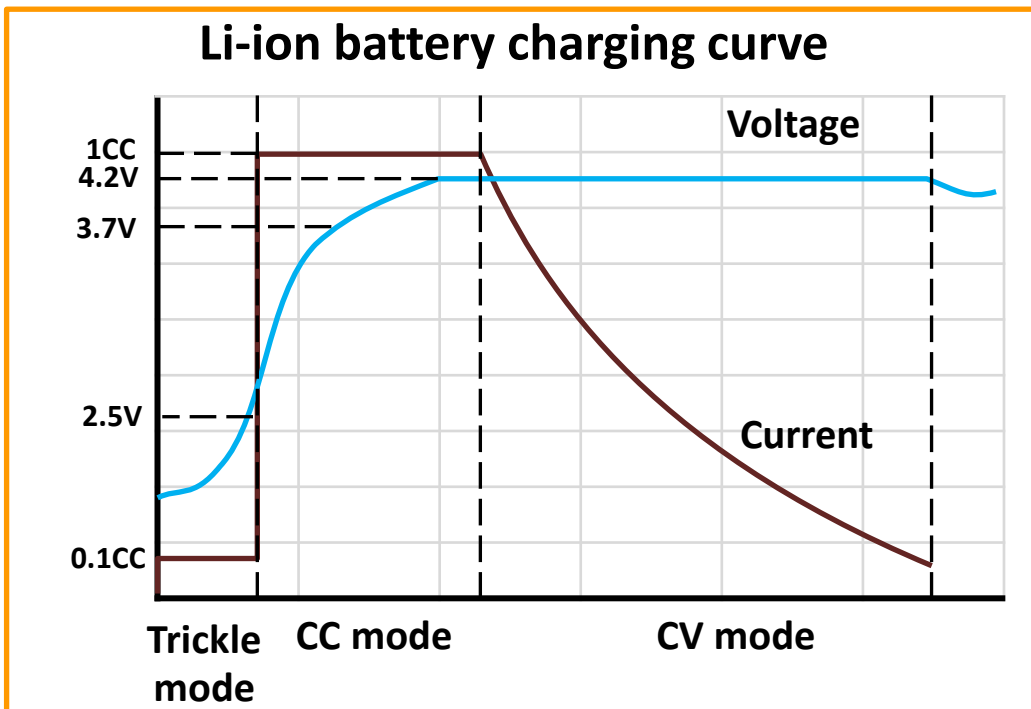
When $V_{GS}=0$, BVdss causes a significant I_{DS} to flow.

1. Short Gate and Source.
2. Increase V_{DS} until I_{DS} starts to flow and reaches the specified value, at which point V_{DS} is measured.



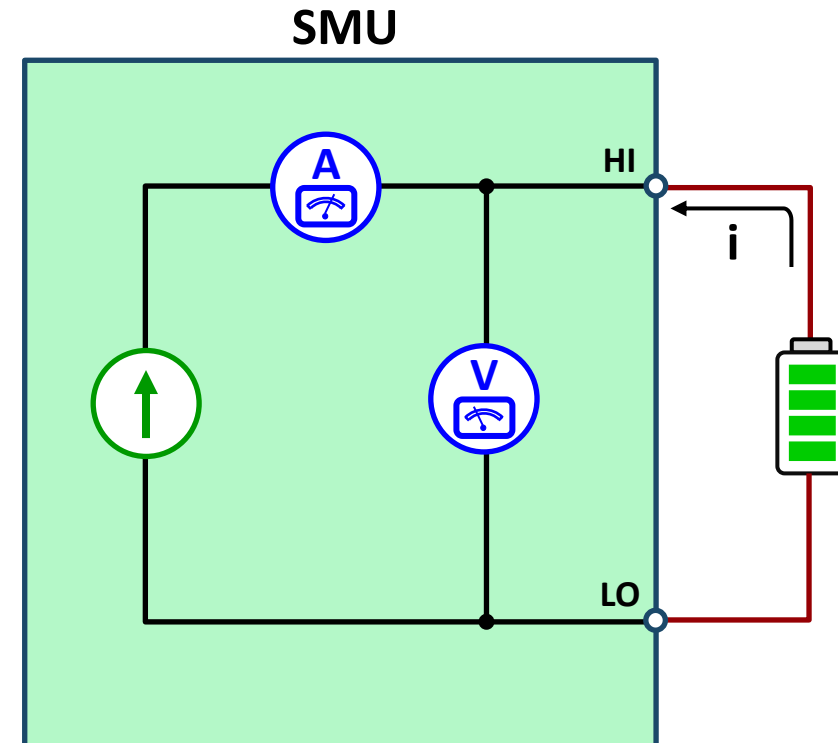
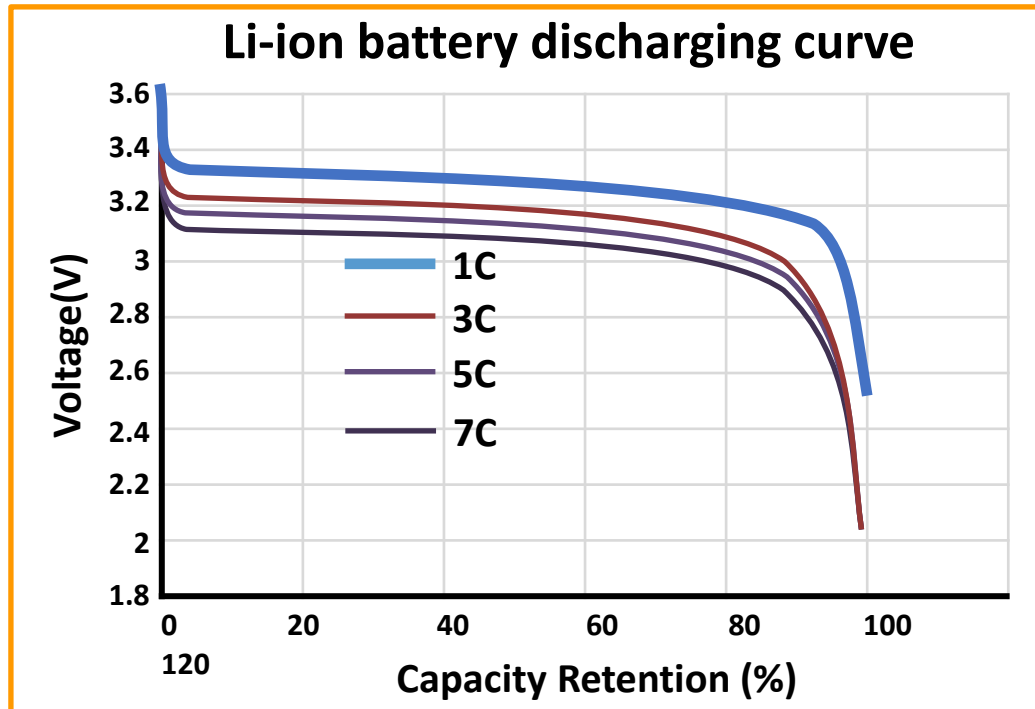
Battery charging test

- SMU as voltage and current source
- SMU voltage > Battery voltage
- Current flows from SMU to battery



Battery discharging test

- SMU as a load
- SMU voltage < Battery voltage
- Current flows from battery to SMU

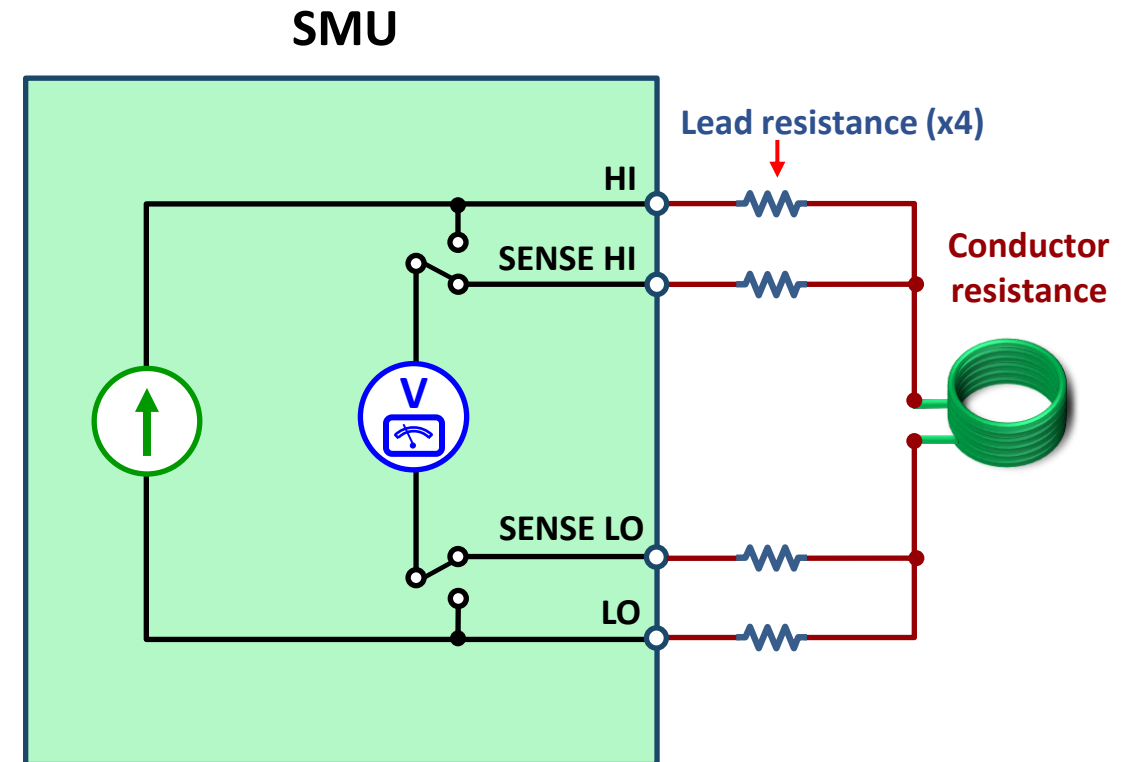


Low resistance measurement

- Example: conductor resistance measurement.

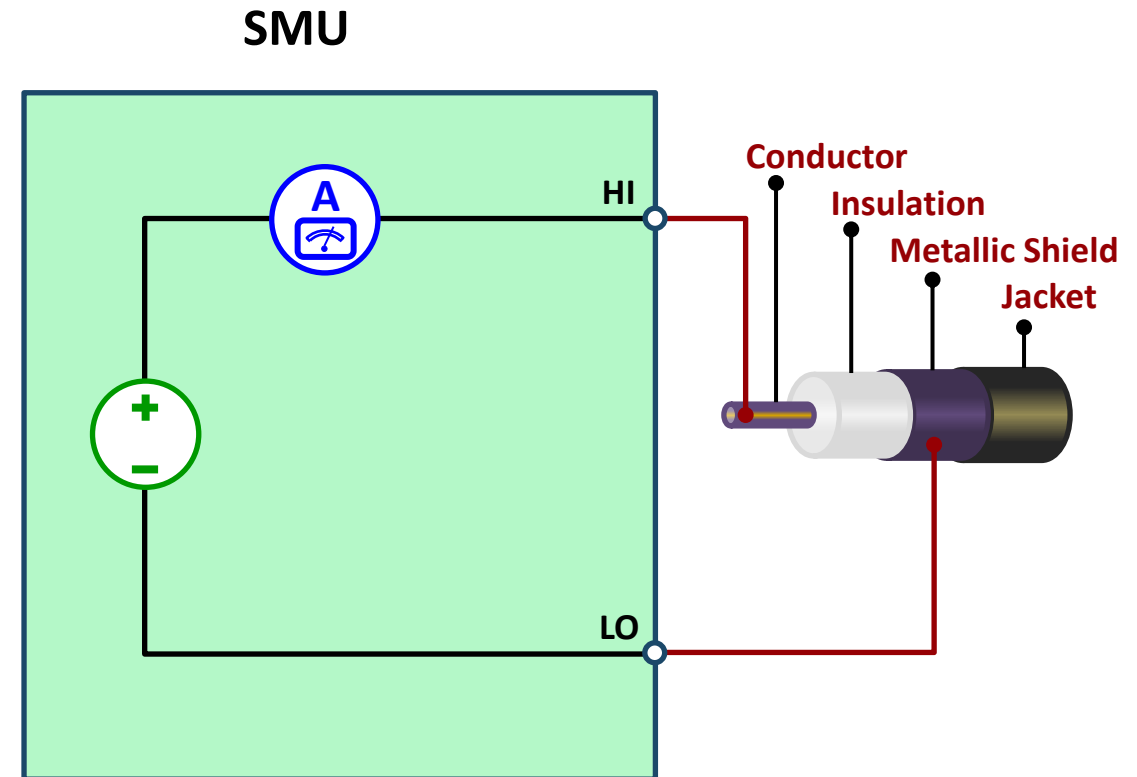
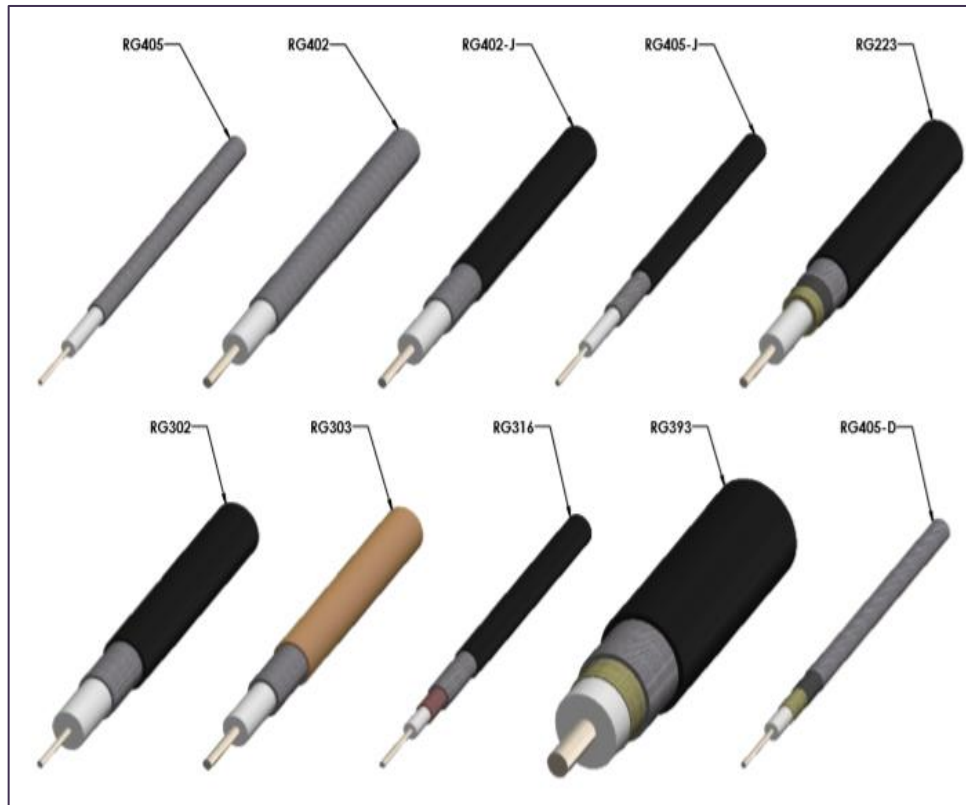


Wire Resistance Chart (20°C)				
Gauge (AWG)	Diameter (in)	Diameter (mm)	Resistance (Ω /ft)	Resistance (Ω /m)
28	0.0126	0.3211	5.29	17.35
29	0.0113	0.2859	6.92	22.69
30	0.0100	0.2546	8.83	29.30
31	0.0089	0.2268	10.01	32.85
32	0.0080	0.2019	13.29	43.60
33	0.0071	0.1798	19.21	63.01
34	0.0063	0.1601	24.69	81.00
35	0.0056	0.1426	27.76	91.07
36	0.0050	0.1270	35.00	114.84



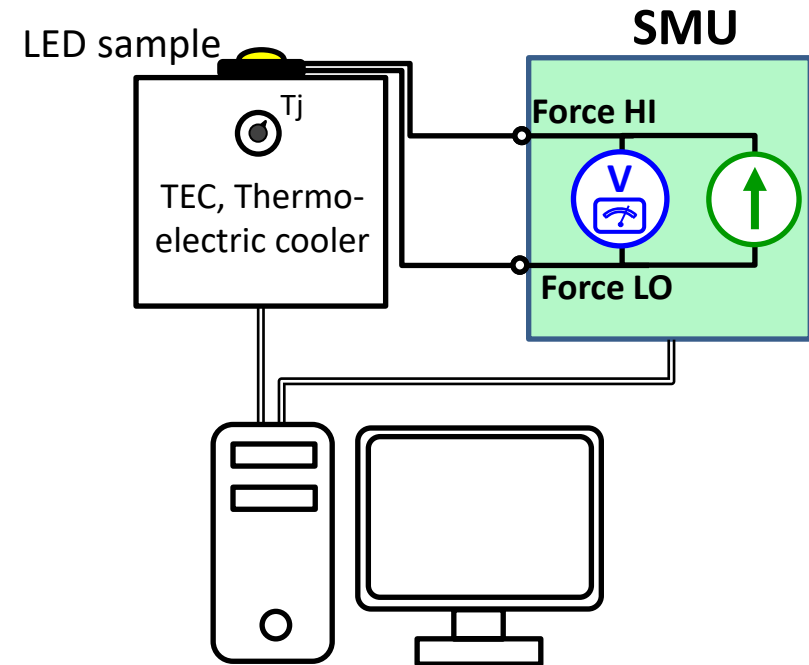
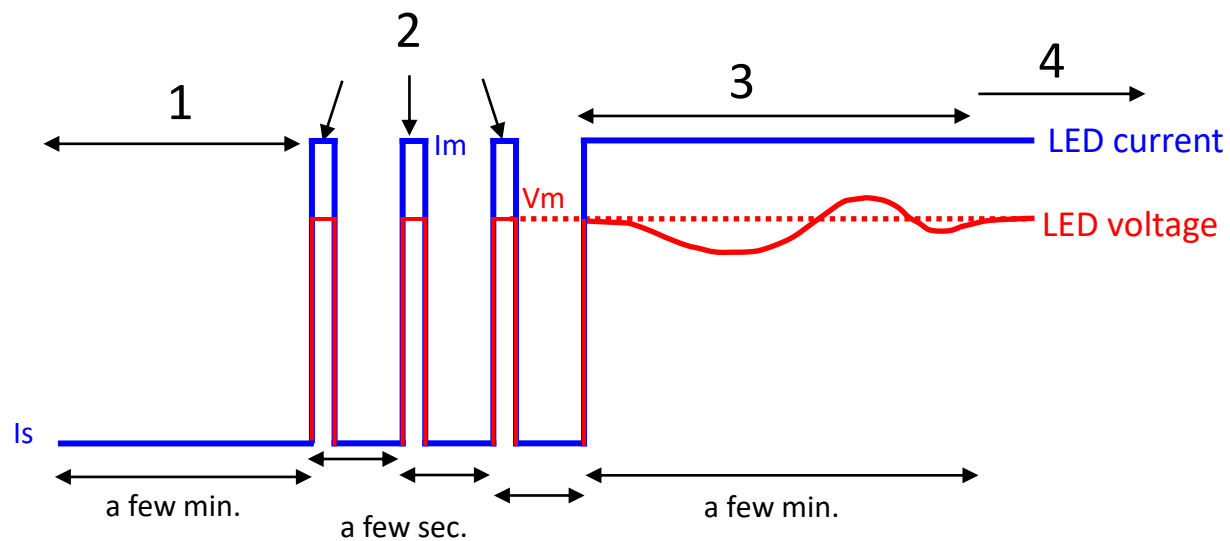
Insulation resistance measurement

- Example: Cable insulation resistance measurement.



LED – Thermal resistance measurement

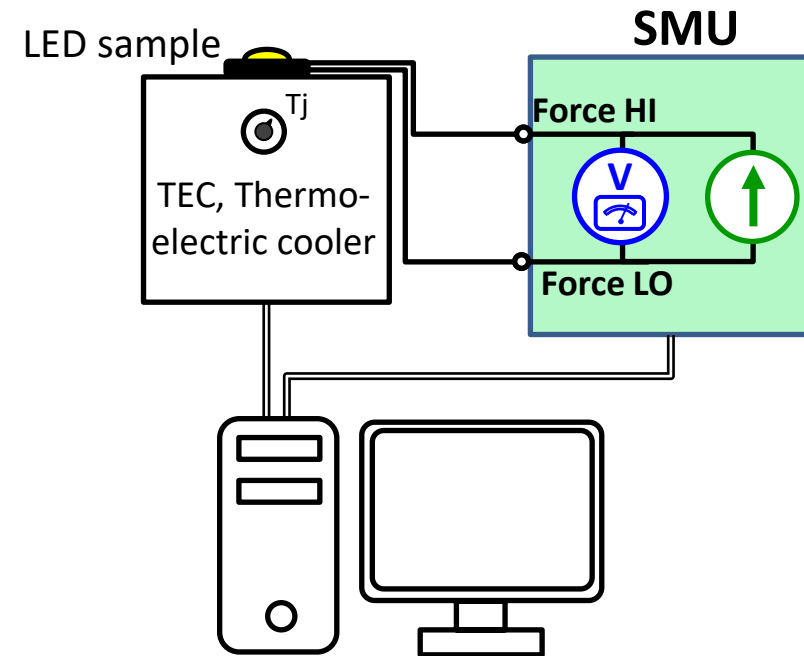
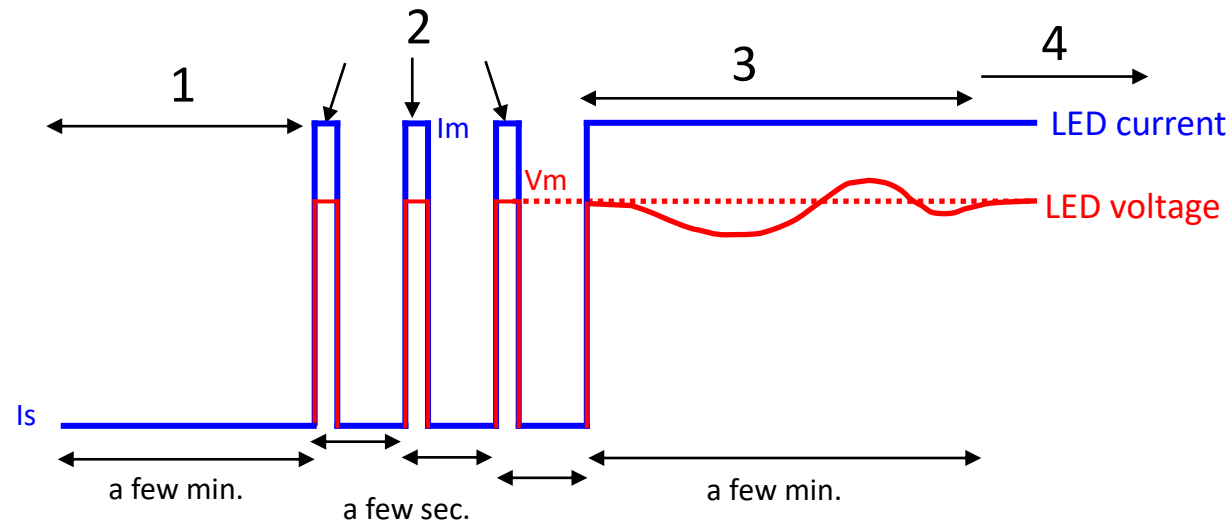
1. Set LED sample temperature at T_j . SMU outputs a small current I_s .
2. SMU outputs pulse current I_m . Measure voltage and record as V_m .
3. Alter output to DC current. Tune the LED temperature to stabilize voltage to V_m .



LED – Thermal resistance measurement

1. Set LED sample temperature at T_j . SMU outputs a small current I_s .
2. SMU outputs pulse current I_m . Measure voltage and record as V_m .
3. Alter output to DC current. Tune the LED temperature to stabilize voltage to V_m .
4. Record temperature as T_m . Calculate R_t .

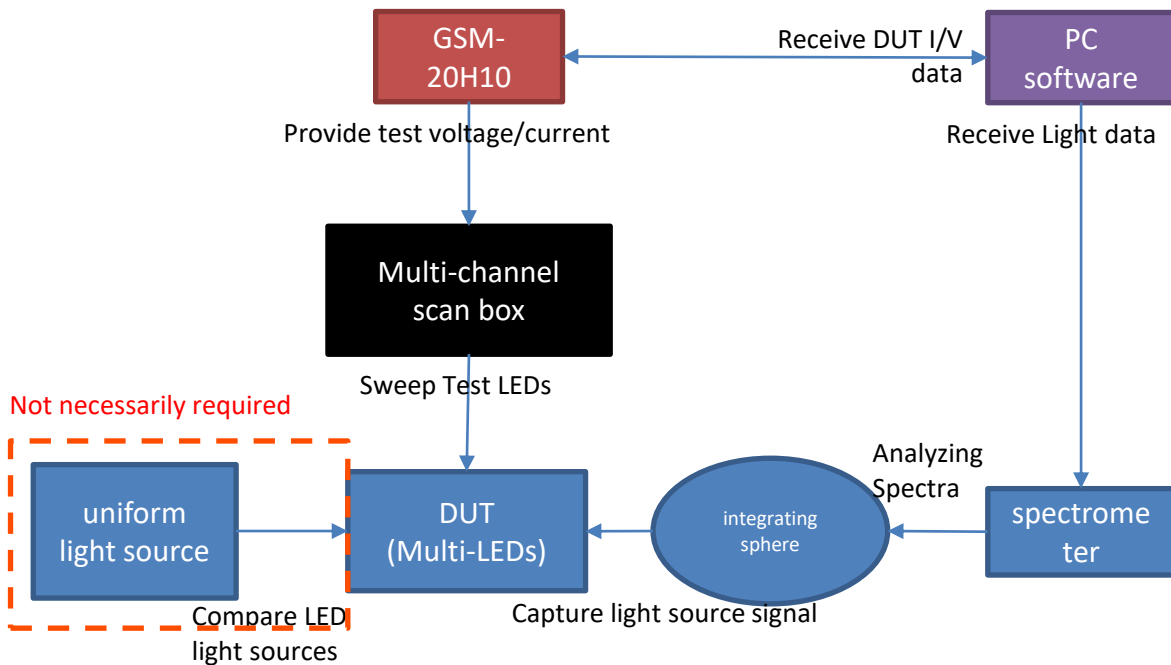
$$R_t = \frac{|T_j - T_m|}{V_m \times I_m}$$



Successful Story in Taiwan

LIV Test System (with Tempoint Corp. in TW)

- LIV (Light-Current-Voltage)



可程式多通道光電檢測系統

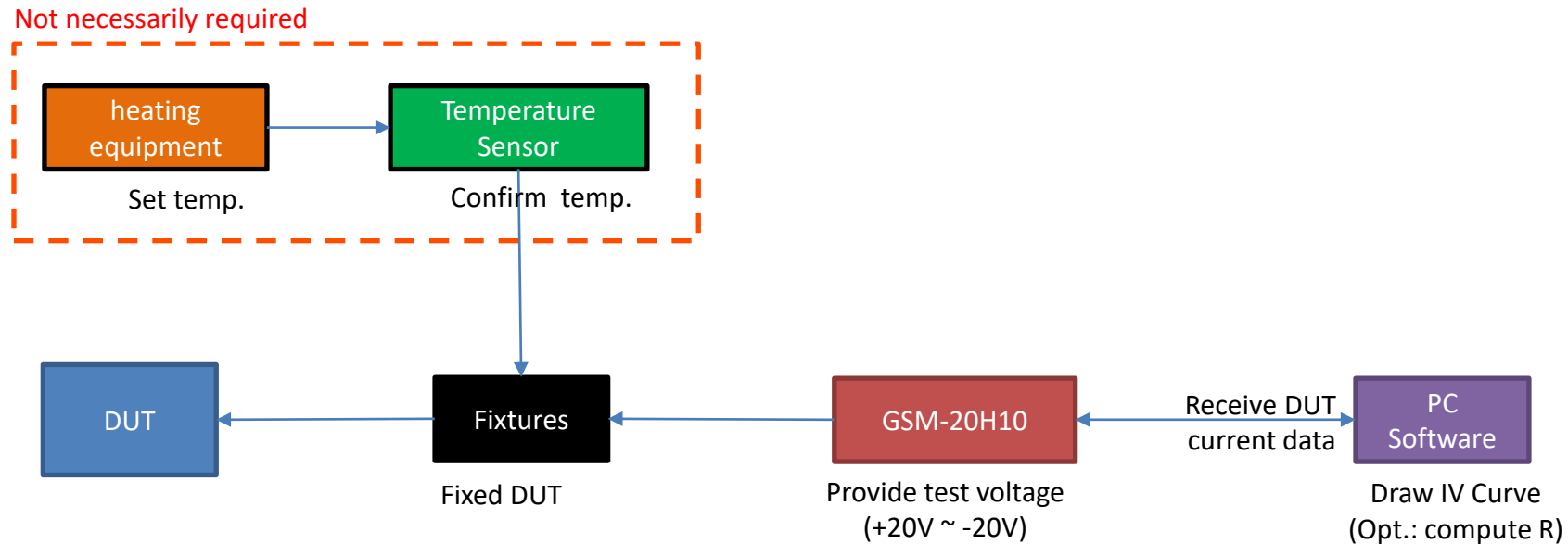
應用: VCSEL, UV LED, 負載測試, 可靠度驗證

The photograph shows the physical components of the LIV Test System: a **積分球** (Integrating Sphere), a **標準可調色溫均勻光源** (Standard adjustable color temperature uniform light source), a **光譜儀** (Spectrometer) with a **USB2000+** interface, and a **多通道掃描盒** (Multi-channel scan box). A computer monitor displays the **PC software** interface, which includes a spectral graph and a color calibration chart.

利用積分球、光譜儀搭配源表進行光源測試，如 LED 光電特性測試等。並可透過多通道掃描盒與系統介接來提升測試效率。

Material Test (Plated Sheet)

- IV (Current-Voltage)

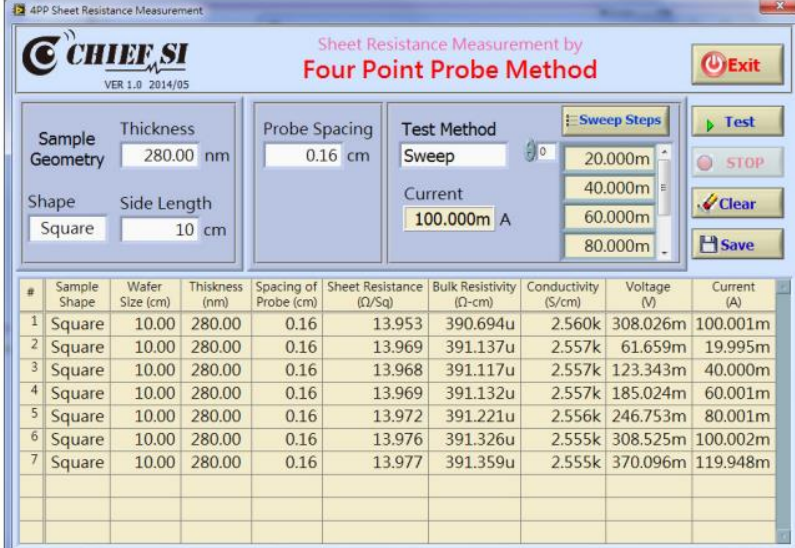


Note: This type of test will also be used to test other materials that require exposure.

Four-Point Probe Sheet Resistance Measurement

System Features:

- User-friendly and intuitive software interface
- Precisely measure the thin film resistance of the DUT
- Constant current measurement. Single-point measurement or multi-point scanning can be selected
- When the thickness of the film is known, the bulk resistivity and conductivity are calculated at the same time
- Adopt .CSV file storage format, which is convenient for users to process data
- Compatible with Keithley 2400-SMU GSM-20H10. It can also be customized with various SMUs and micro- and high-resistance meters according to user needs.

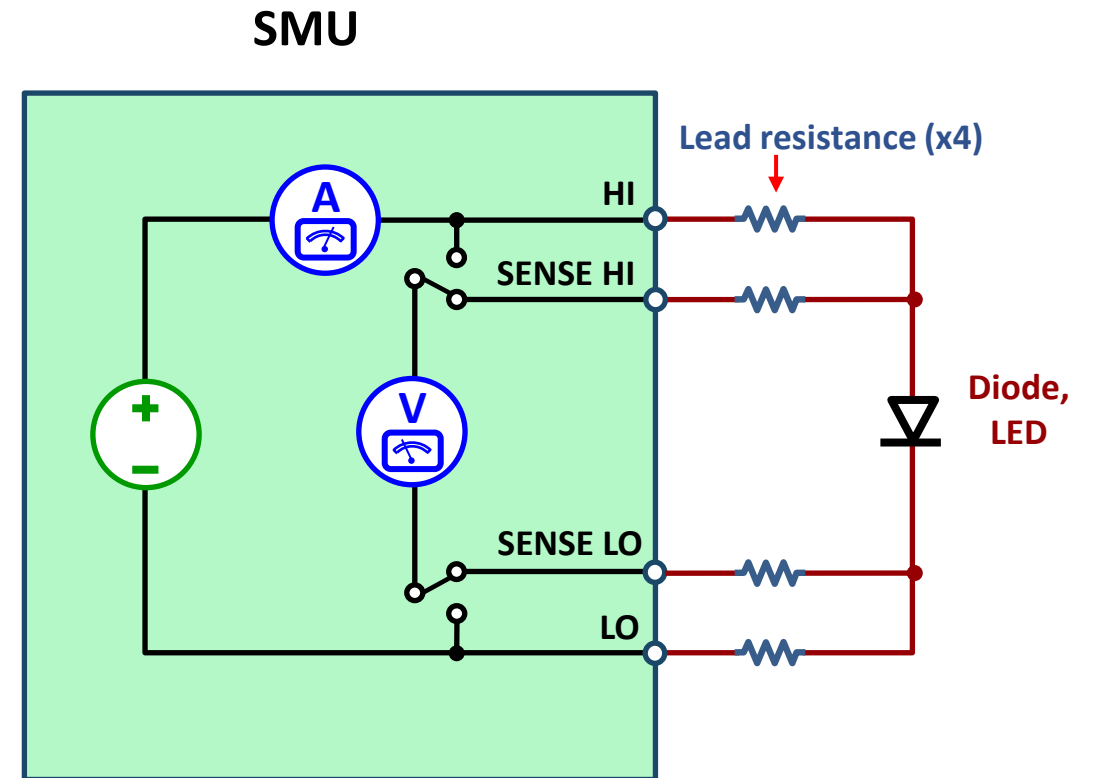
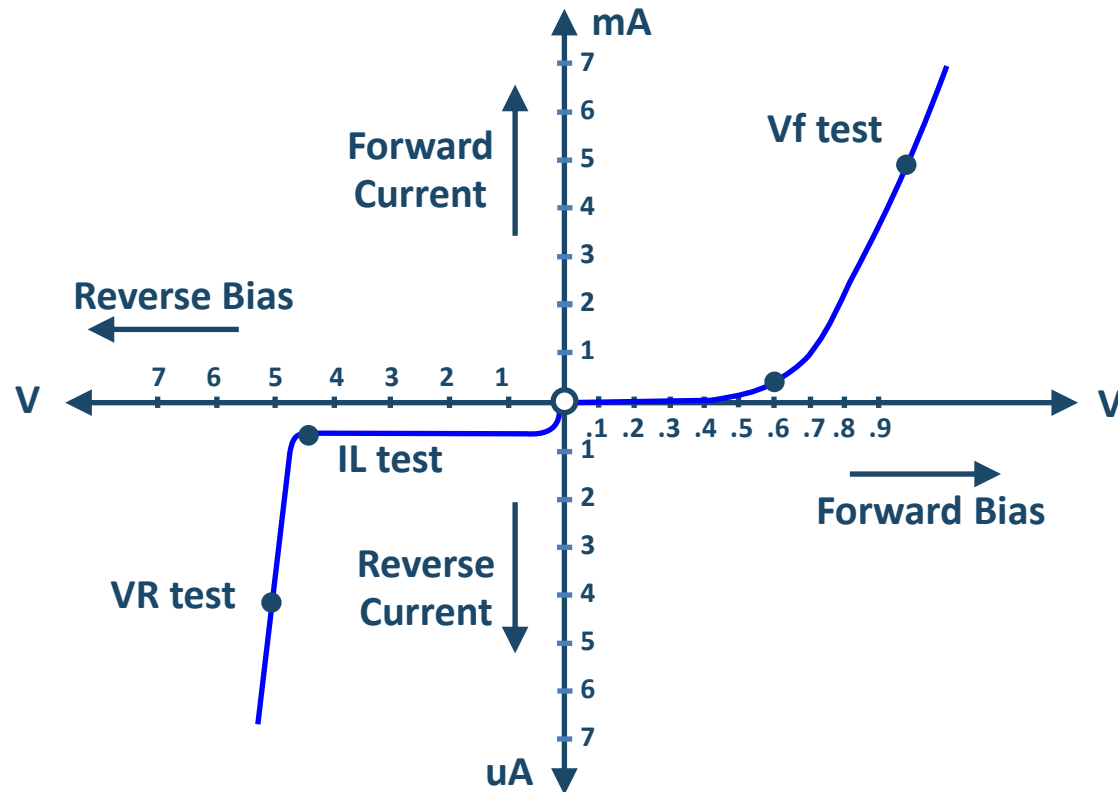


#	Sample Shape	Wafer Size (cm)	Thickness (nm)	Spacing of Probe (cm)	Sheet Resistance (Ω/Sq)	Bulk Resistivity (Ω-cm)	Conductivity (S/cm)	Voltage (V)	Current (A)
1	Square	10.00	280.00	0.16	13.953	390.694u	2.560k	308.026m	100.001m
2	Square	10.00	280.00	0.16	13.969	391.137u	2.557k	61.659m	19.995m
3	Square	10.00	280.00	0.16	13.968	391.117u	2.557k	123.343m	40.000m
4	Square	10.00	280.00	0.16	13.969	391.132u	2.557k	185.024m	60.001m
5	Square	10.00	280.00	0.16	13.972	391.221u	2.556k	246.753m	80.001m
6	Square	10.00	280.00	0.16	13.976	391.326u	2.555k	308.525m	100.002m
7	Square	10.00	280.00	0.16	13.977	391.359u	2.555k	370.096m	119.948m

*Sheet Resistance
Measurement*

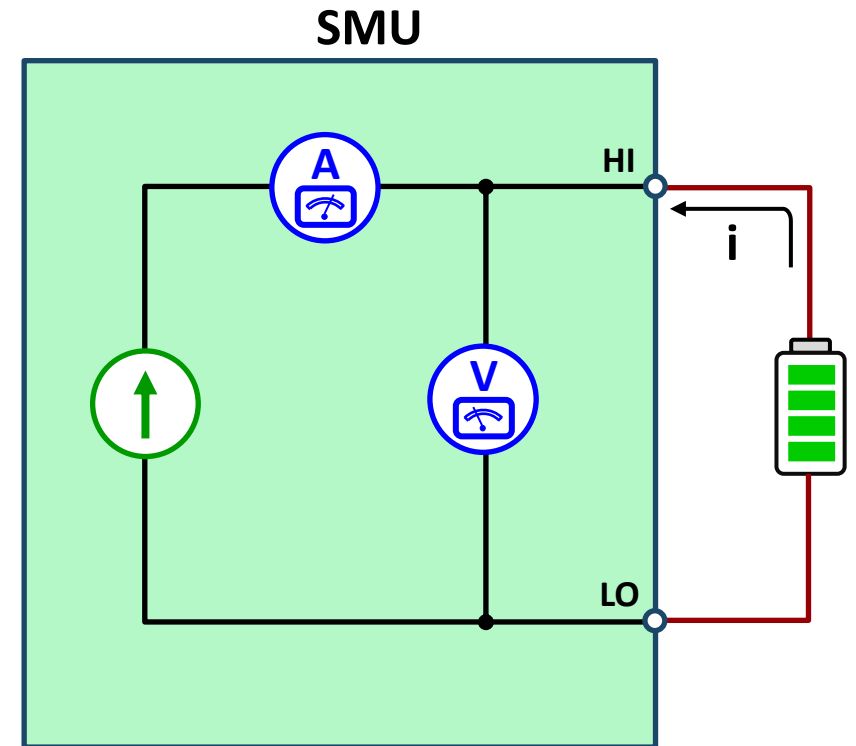
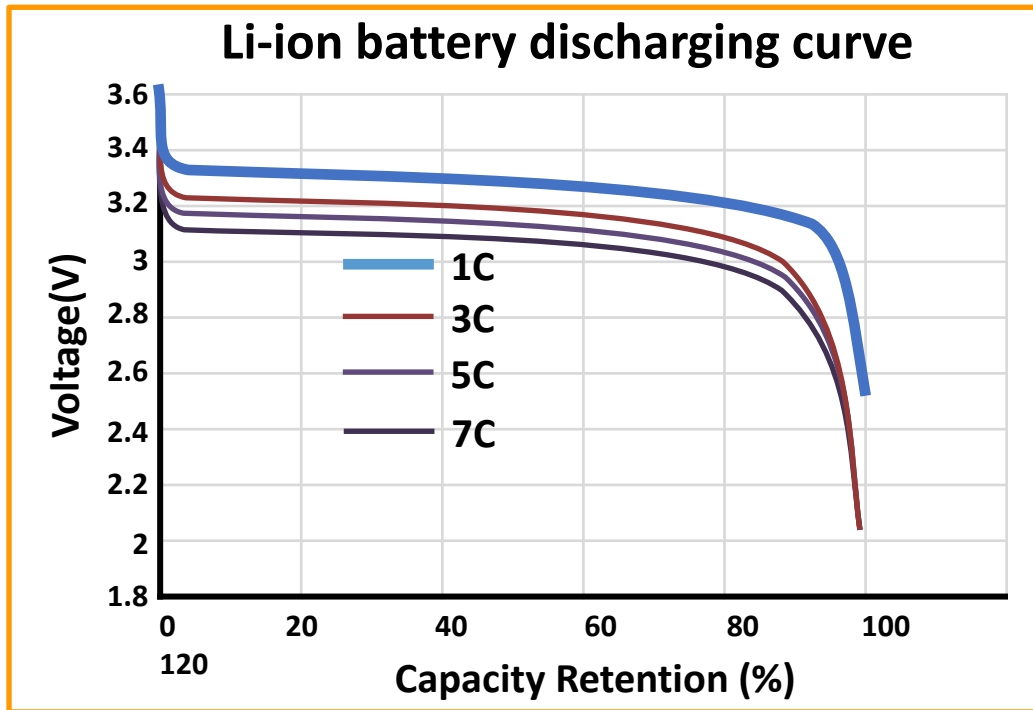


UVLED V-I characteristics test (by Tom)



Battery discharging test

- Battery discharging test (Department of Earth Sciences of NCU)



GRACIAS
ARIGATO
SHUKURIA
GOZAIMASHITA
EFCHARISTO
JUSPAXAR
DANKSCHEEN
SPASSIBO
SNACHALHUYA
NUHUN
CHALTU
YAQHANYELAY
TASHAKKUR ATU
WABEEJA
MAITEKA
HUI
YUSPAGARATAM
SUKSAMA
EKHMET
ATTO
ANHA
DHANYADAAD
MIRSI
SPASIBO
DENKAUJA
HENACHALHYA
UNALCHEESH
HATUR
TINGKI
BIYAN
SHUKRIA
GRAZIE
MEHRBANI
PALDIES
YOU
BOLZIN
MERCI
MAAKE
LAH
KOMAPSUMNIDA
SAVCO
MERASTAMHY
GAEJTHO
AGUYJE
FAKAUE
MINMONCHAR
MAKETAI
EKOJU
SIKOMO